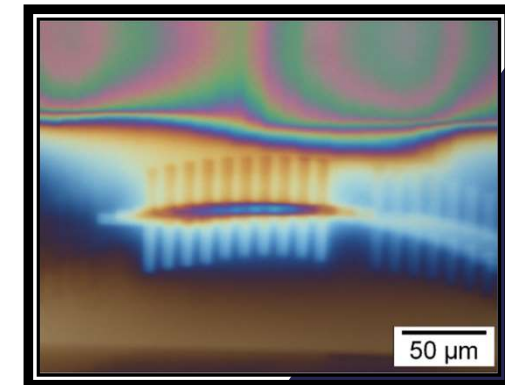
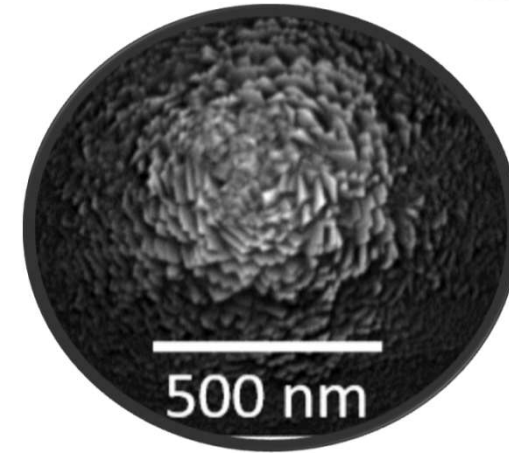
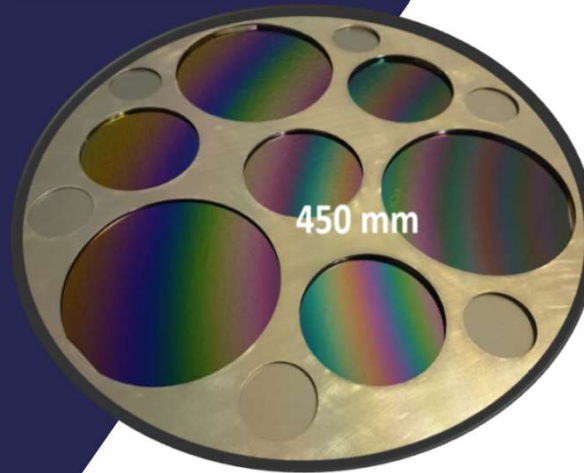


CHEMICAL BEAM EPITAXY LASER-ASSISTED Sybilla equipment

Giacomo Benvenuti, PhD.

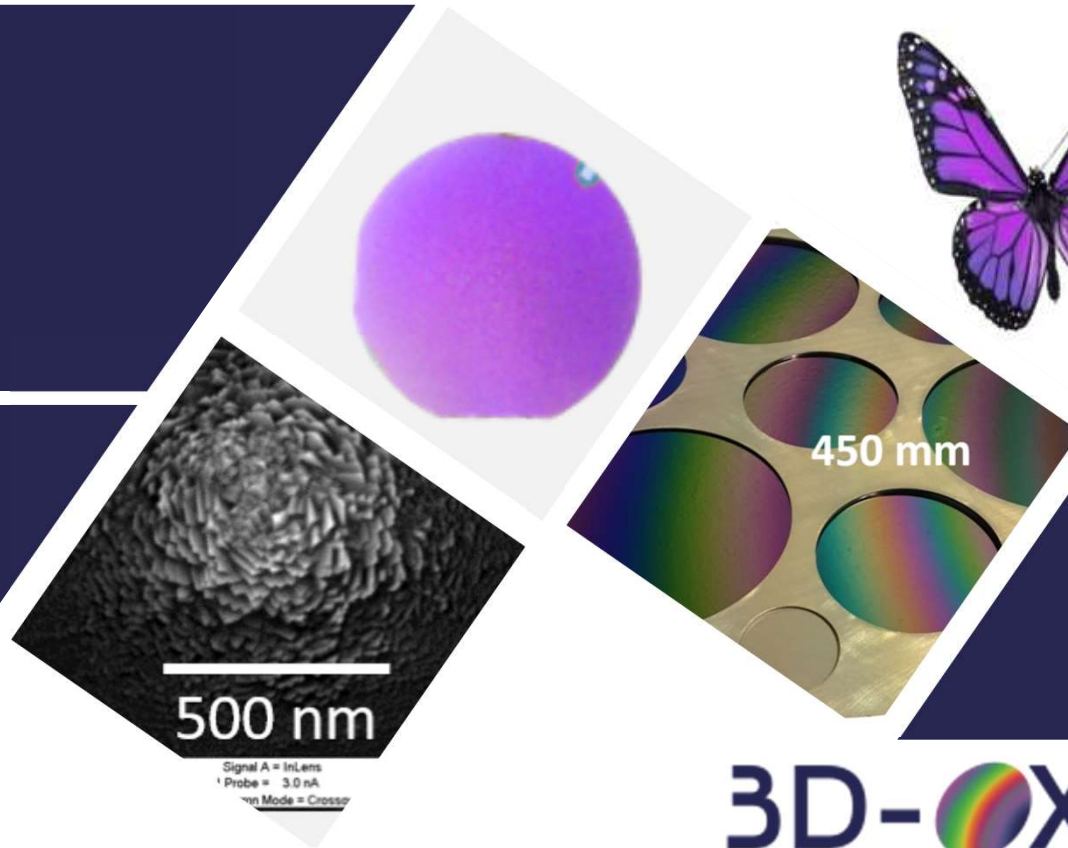
E. Wagner (PhD),
S.C. Sandu (PhD),
W. Maudez (PhD),
S. Bagdzevicius (PhD),
R. Rani (PhD)



WHY WE NEED A NEW TOOL?
CBE-CBVD & SYBILLA EQUIPMENT
COMBINATORIAL GROWTH
ADDITIVE GROWTH
SOME FUNCTIONAL MATERIALS
CONCLUSION & OUTLOOK



GLOBAL CONTEXT & 3D-OXIDES



3D-OXIDES
MULTI-FUNCTIONAL THIN FILMS

OXIDE THIN FILMS OFFER UNIQUE OPPORTUNITIES

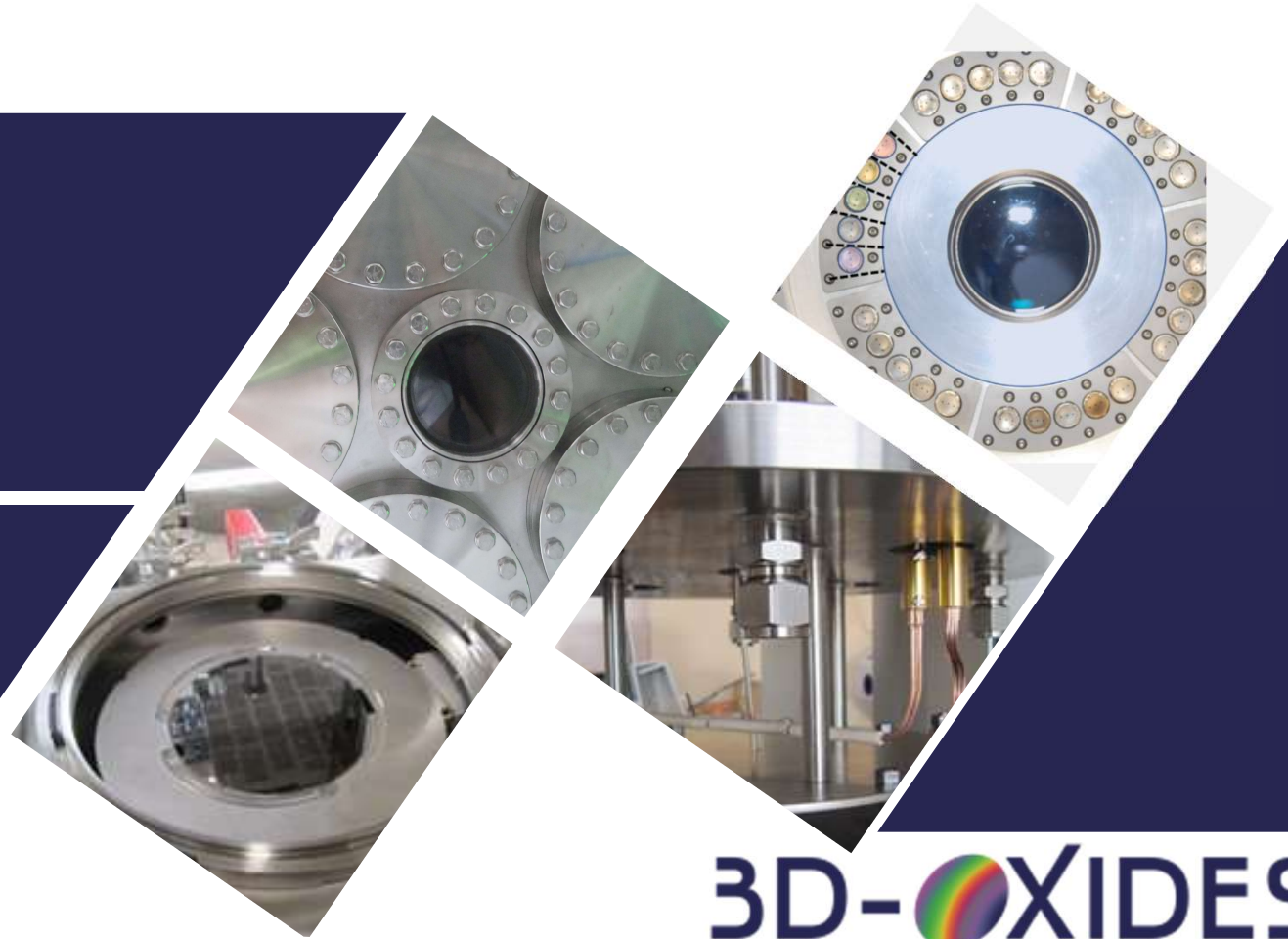
- Replace scarce or toxic elements
- Multi-functional materials for new devices (More than Moore)

HOWEVER, THEY ARE FAR MORE COMPLEX !

- Huge amount of combinations
- Higher temperatures for epitaxy and crystals quality
- Strong material properties variations for non perfect crystals
- Complex Figures of Merit for multi-functional materials

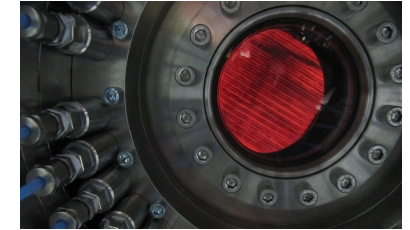
CHEMICAL BEAM EPITAXY LASER-ASSISTED (CBE-LA)

SYBILLA EQUIPMENT



3D-OXIDES
MULTI-FUNCTIONAL THIN FILMS

CHEMICAL PRECURSORS IN MOLECULAR VACUUM



CBE vs. PVD TECHNIQUES

- Chemical selectivity (2 different regimes)
- Lower process temperatures
- Less sensitive to gas contamination (reduced getter effects)
- Small gas sources for better control



CBE vs. CVD TECHNIQUES

MOLECULAR Vacuum

- No gas phase reaction
- No boundary layers with slow diffusive processes
- Line of sight & easy impinging rates modeling
- UHV characterization techniques
- Beam-assisted deposition & use of very reactive species

- Chemistry
- Complex multi-parameter process



- Reduced number of available precursors

AVAILABLE CHEMICAL PRECURSORS

| | | | | | | | | | | | | | | | | | |
|----|----|----|----|----|----|----|----|----|----|----|-----|-----|-----|-----|-----|-----|-----|
| H | | | | | | | | | | | | | | | | | He |
| Li | Be | | | | | | | | | | | B | C | N | O | F | Ne |
| Na | Mg | | | | | | | | | | | Al | Si | P | S | Cl | Ar |
| K | Ca | Sc | Ti | V | Cr | Mn | Fe | Co | Ni | Cu | Zn | Ga | Ge | As | Se | Br | Kr |
| Rb | Sr | Y | Zr | Nb | Mo | Tc | Ru | Rh | Pd | Ag | Cd | In | Sn | Sb | Te | I | Xe |
| Cs | Ba | * | Hf | Ta | W | Re | Os | Ir | Pt | Au | Hg | Tl | Pb | Bi | Po | At | Rn |
| Fr | Ra | * | Rf | Db | Sg | Bh | Hs | Mt | Ds | Rg | Uub | Uut | Uuq | Uup | Uuh | Uus | Uuo |

| | | | | | | | | | | | | | | | |
|---|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|
| * | La | Ce | Pr | Nd | Pm | Sm | Eu | Gd | Tb | Dy | Ho | Er | Tm | Yb | Lu |
| * | Ac | Th | Pa | U | Np | Pu | Am | Cm | Bk | Cf | Es | Fm | Md | No | Lr |



Mastered in 3D-oxides



Under investigation in house



Reported in literature



Radioactive, toxic or unstable



Semiconductors in literature

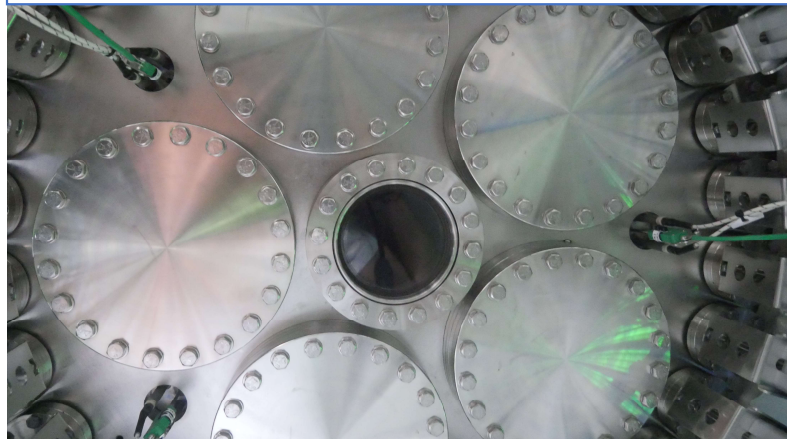


Oxygen plasma

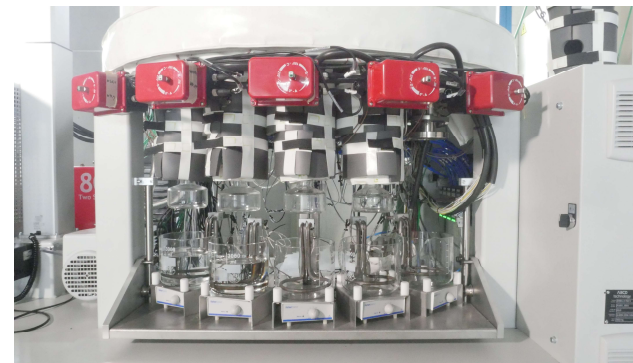
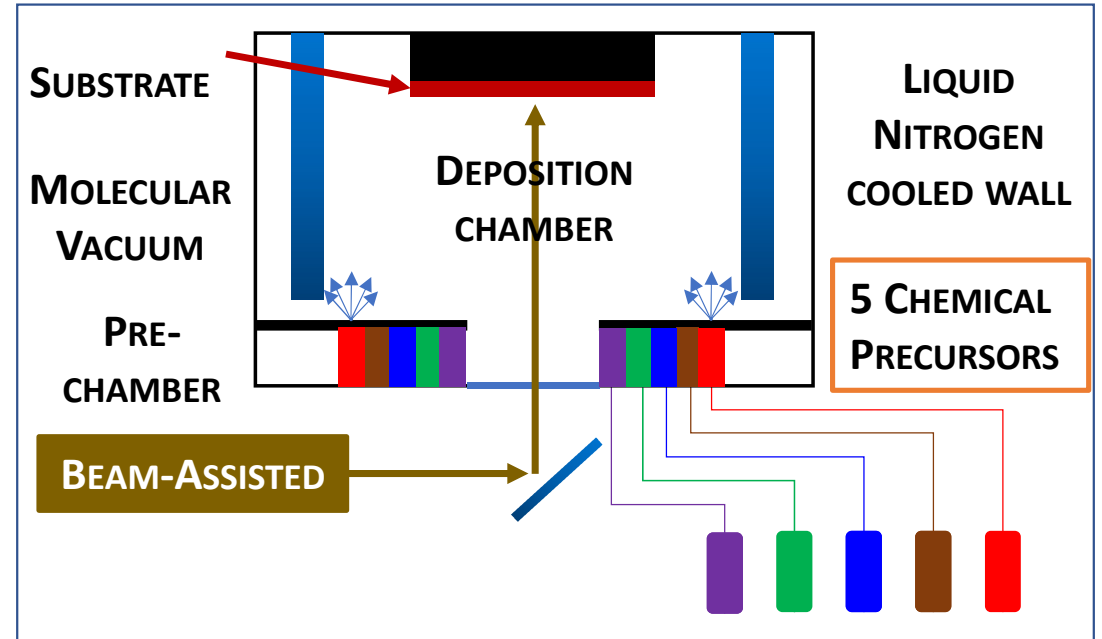
SYBILLA FOR 450 MM SUBSTRATES SET-UP



**SINGLE WAFER SYBILLA-450 MM
MERGING CVD AND MBE ASSETS**

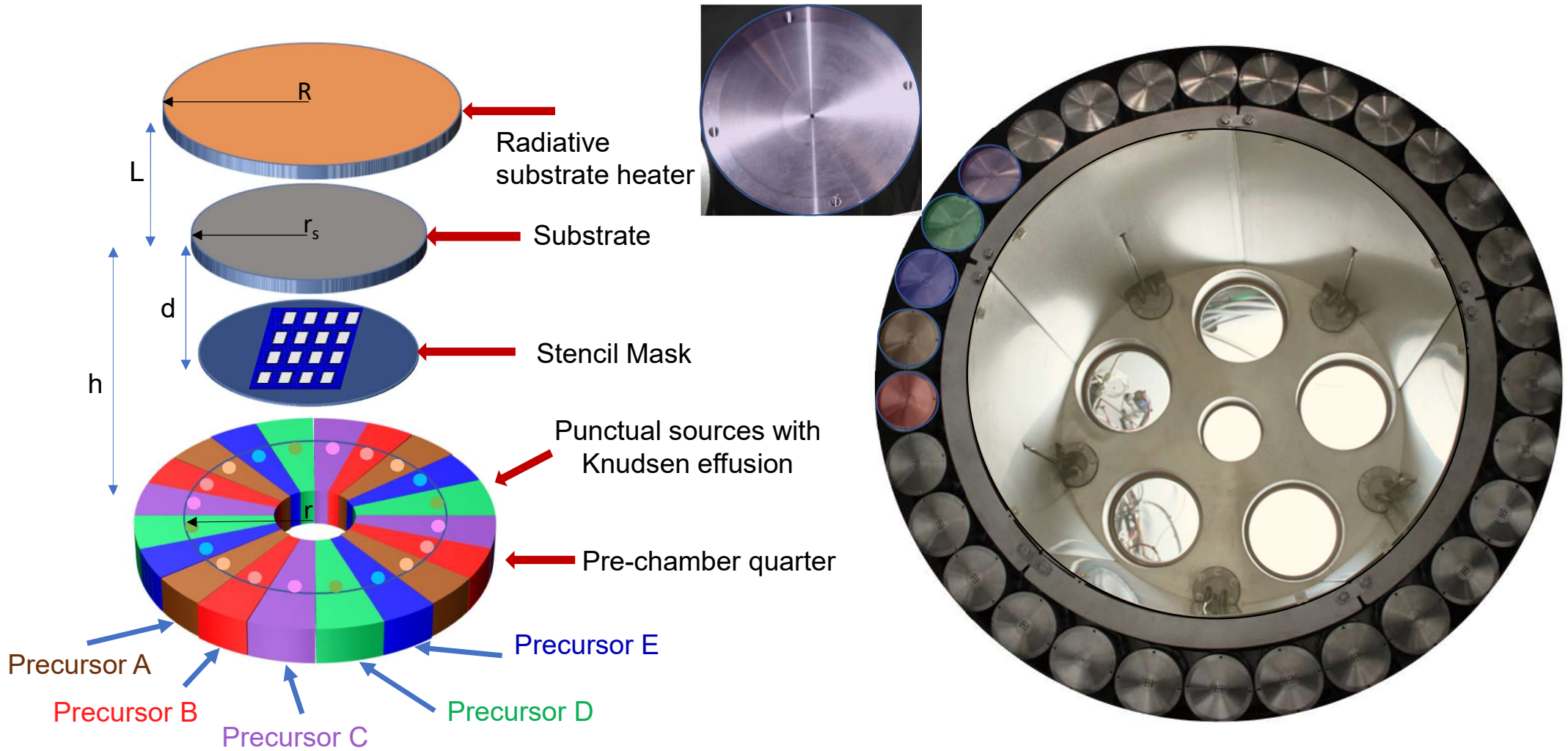


**WINDOWS FOR ASSISTED DEPOSITION OR
CHARACTERIZATION TECHNIQUES**



**5 INDEPENDENT
PRECURSOR SOURCES**

SIDE AND TOP VIEWS OF SYBILLA EQUIPEMENT



SYBILLA (CBE-LA) PERFORMANCES

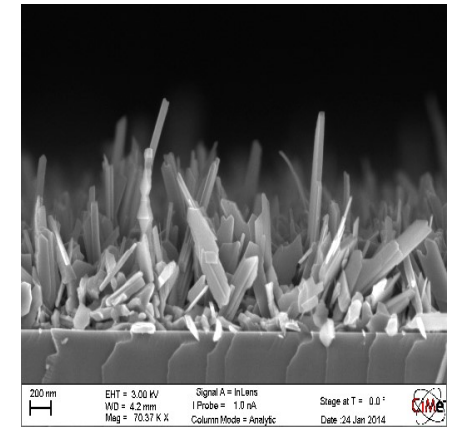
AGILE AND DISRUPTIVE R&D, RELIABLE AND COST EFFICIENT PRODUCTION

| | |
|----------------------------|--|
| Growth rates: | 5 nm h ⁻¹ up to 20 μm h ⁻¹ |
| Layer Quality: | Epitaxial to highly porous thin films |
| Substrate size: | Scalable to any size |
| Number of elements: | Actually 1-5, but scalable to 6 or even more |

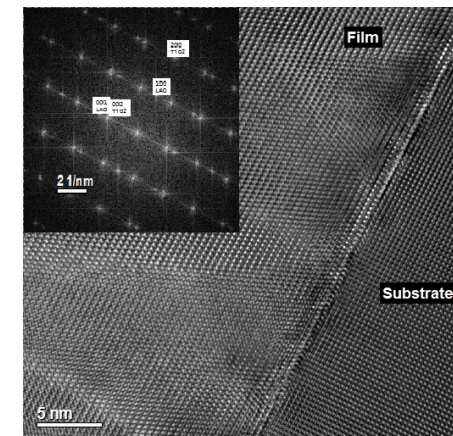
| | |
|--------------------------------|--|
| R&D results uptake: | Very fast as the same equipment is used |
| Process modification: | Very fast: process is not geometry dependent |

| | |
|-----------------------------|--|
| Precursors use: | From 10% up to as high as 65% |
| Equipment life-time: | Extensive (different materials/applications) |
| Costs of ownership: | Possibly lower than few € / cm ² |

| | |
|----------------------------------|---|
| Combinatorial production: | Monolithic integration of ≠ functionalities |
|----------------------------------|---|

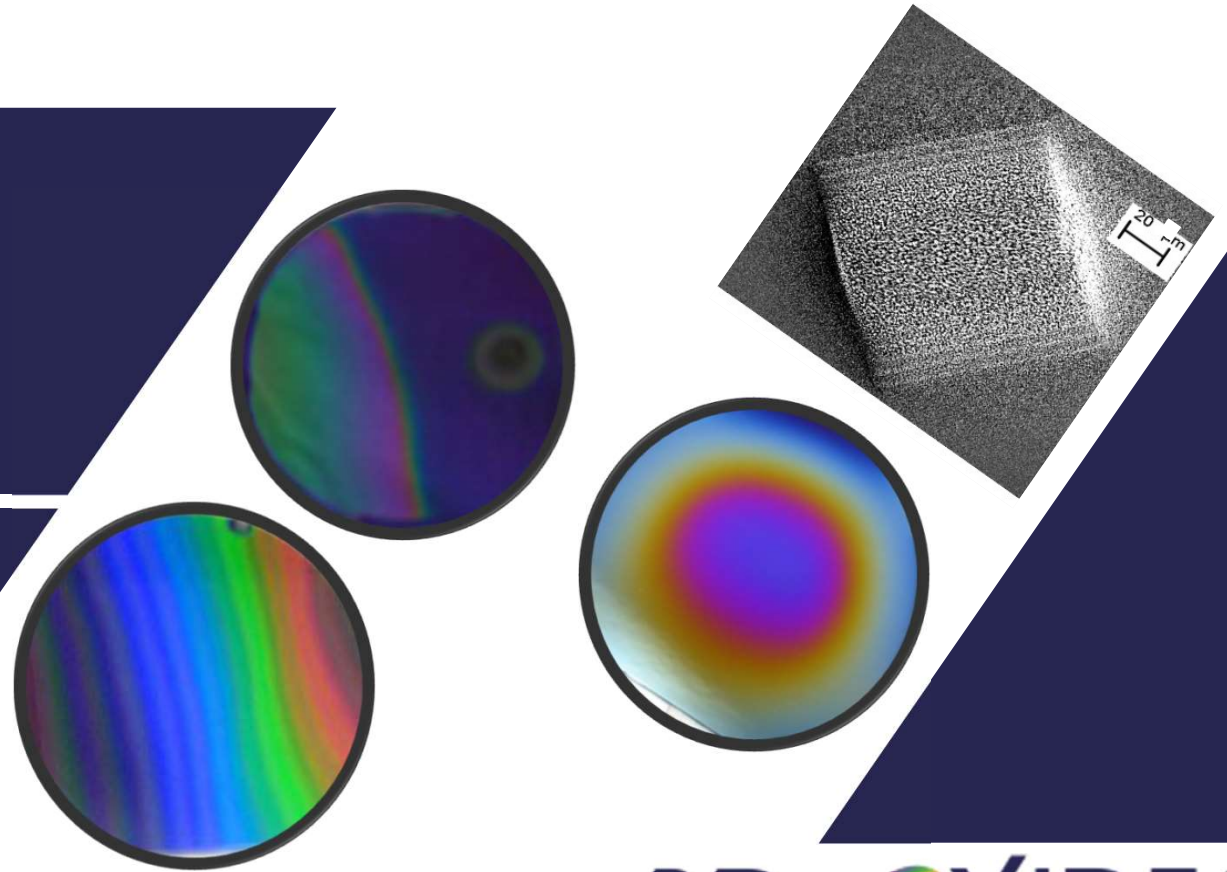


V₂O₅ nano-wires



Epitaxial LiNbO₃

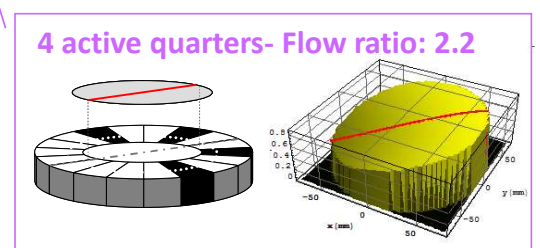
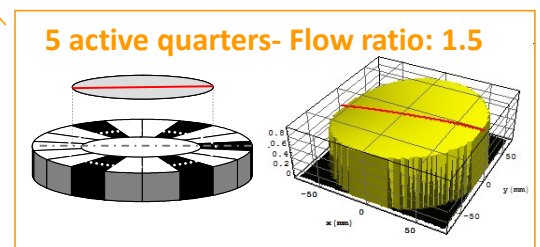
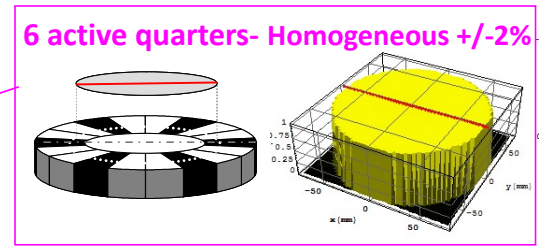
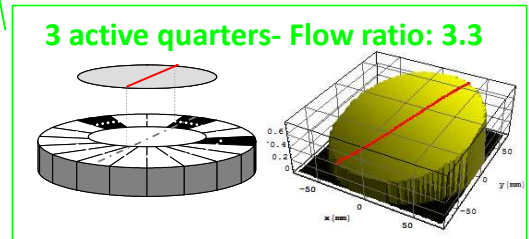
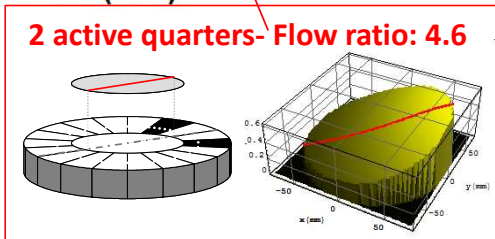
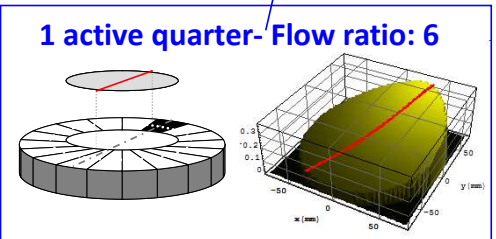
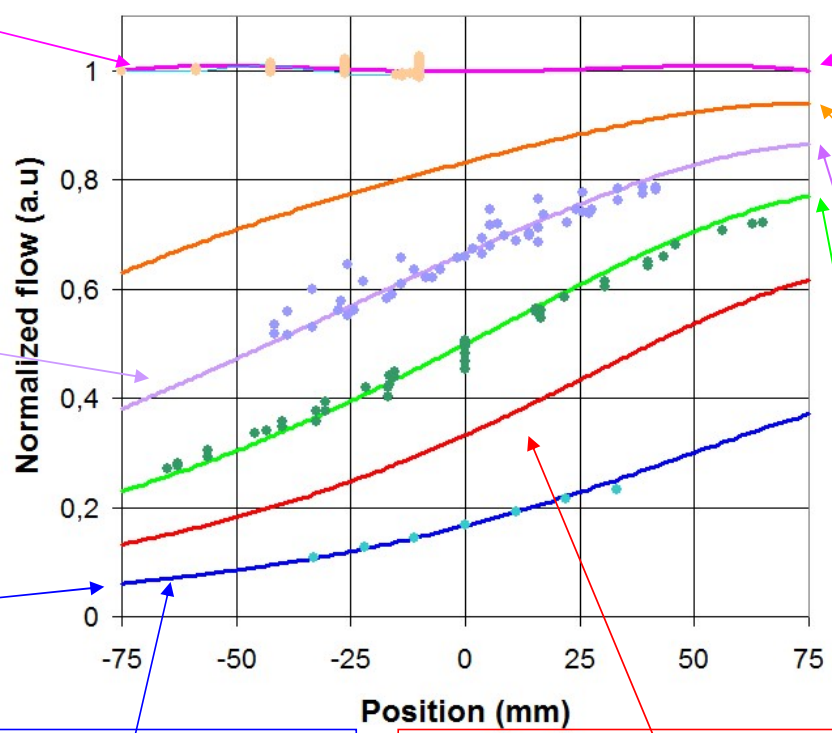
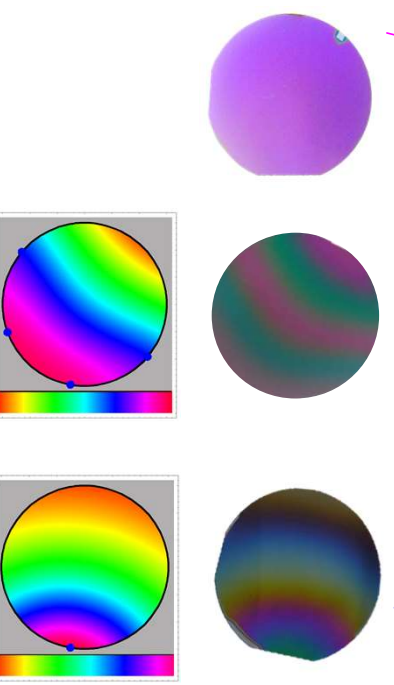
COMBINATORIAL



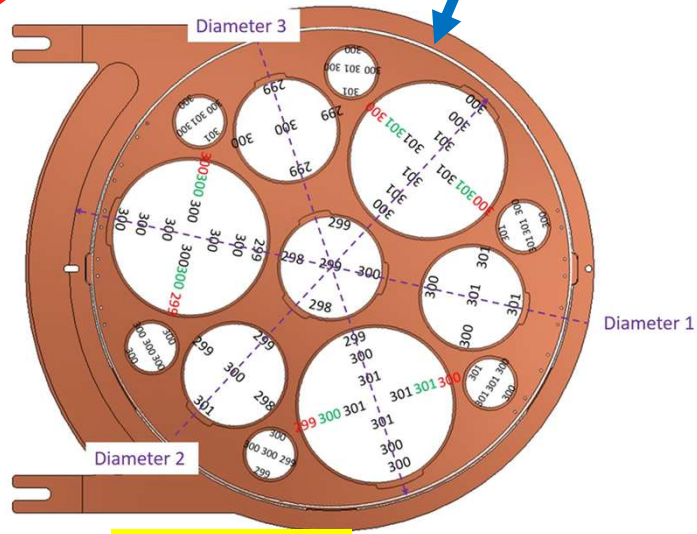
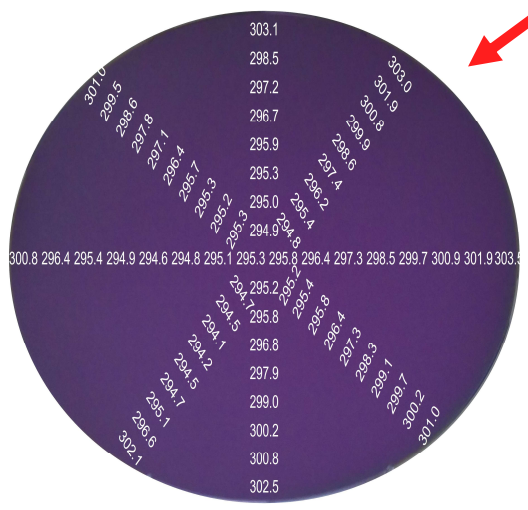
3D-OXIDES
MULTI-FUNCTIONAL THIN FILMS

PRECURSOR FLOW GRADIENTS

Wagner et al. (2016) ACS Combinatorial Science, 18(3) 154

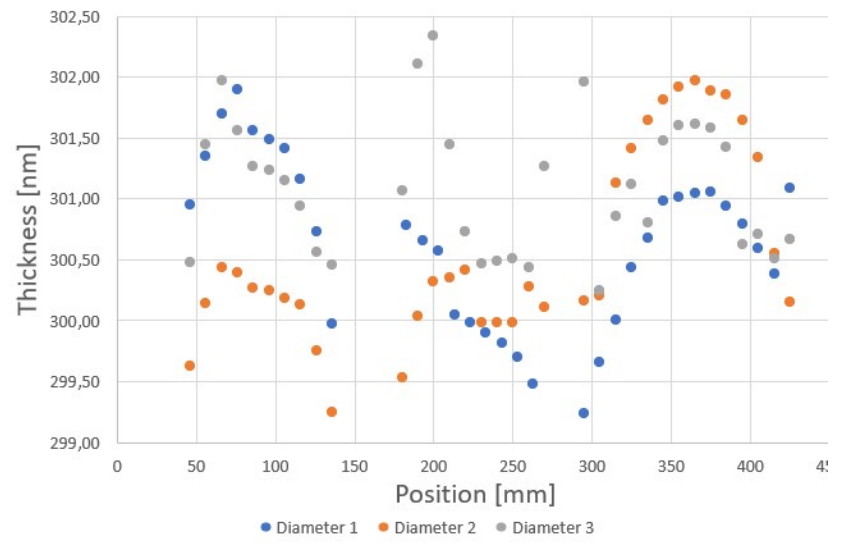


VERY HIGH THICKNESS UNIFORMITY 18" SUBSTRATES



+/- 1,5% uniformity
+/- 0,5% uniformity

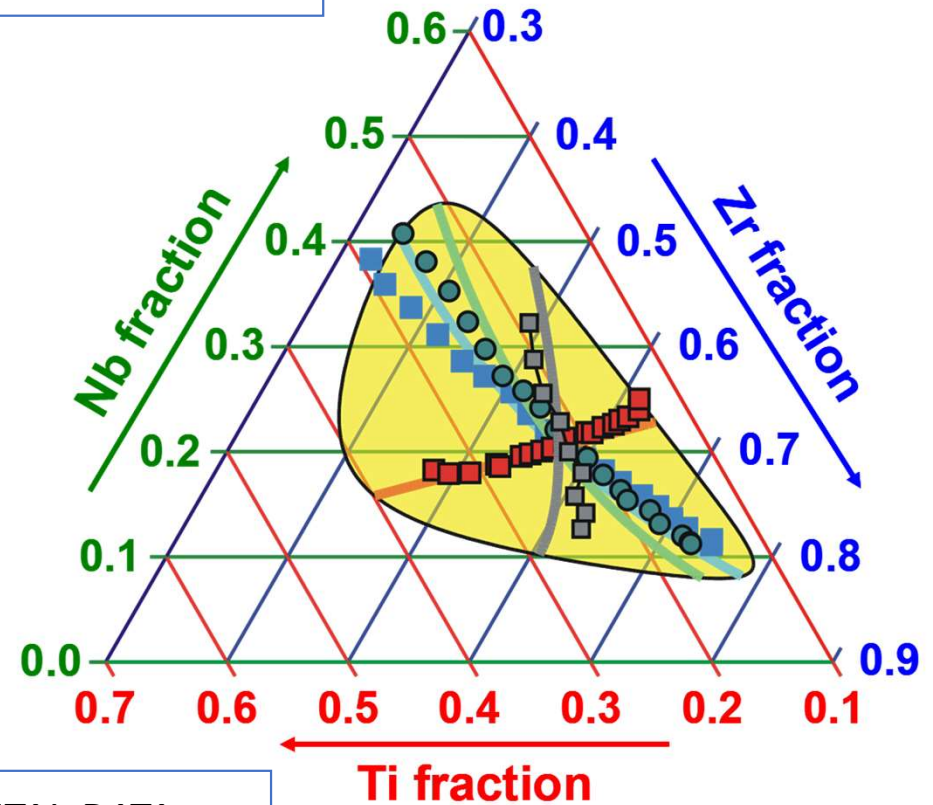
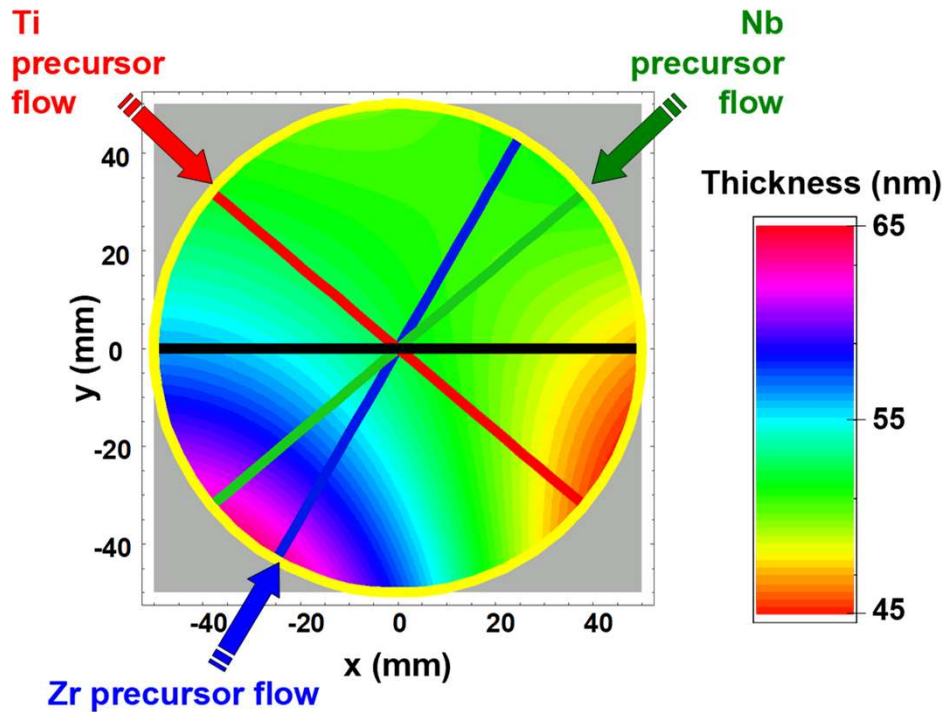
| | All points | Without extrema |
|--------------------|--------------|-----------------|
| min | 299.23 | 299.66 |
| max | 302.34 | 302.34 |
| average | 300.77 | 300.85 |
| sdtv | 0.71127994 | 0.6668543 |
| Homogeneity | 1.03% | 0.89% |



MATERIAL PROPERTIES VS COMPOSITION

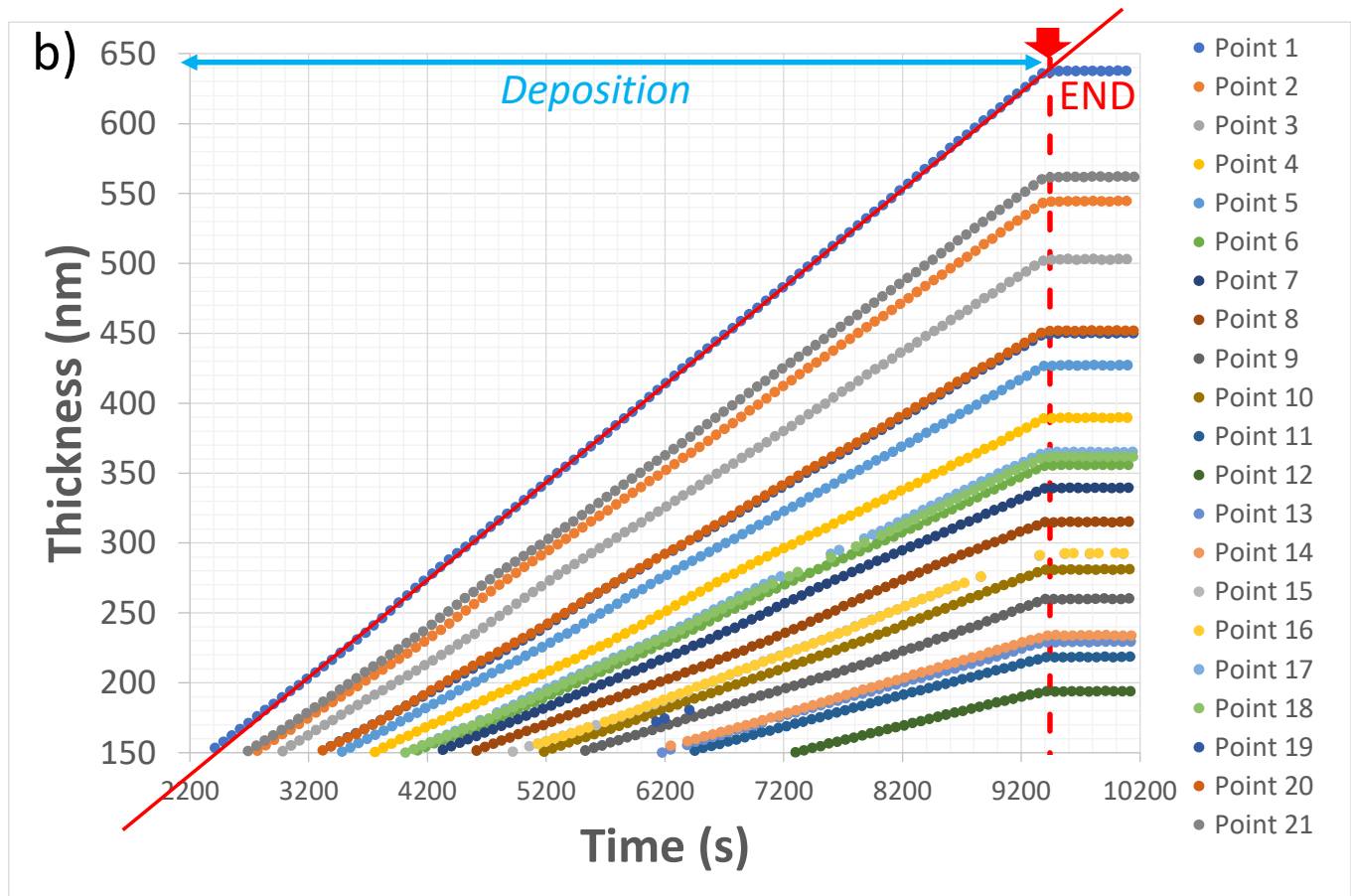
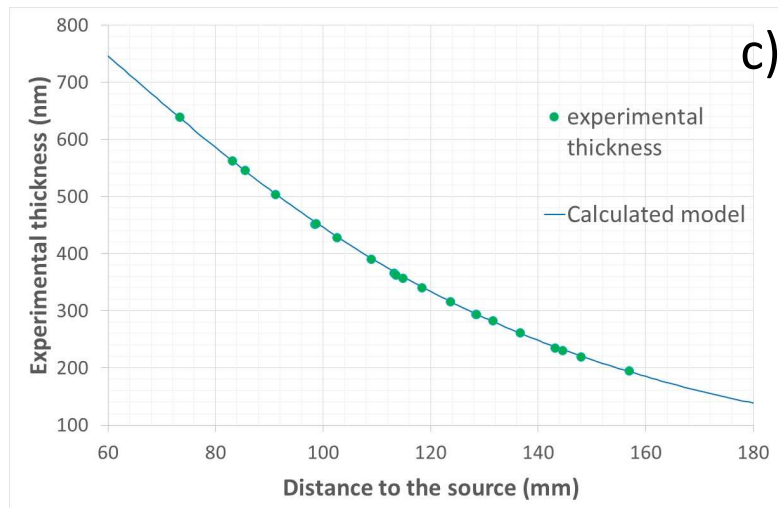
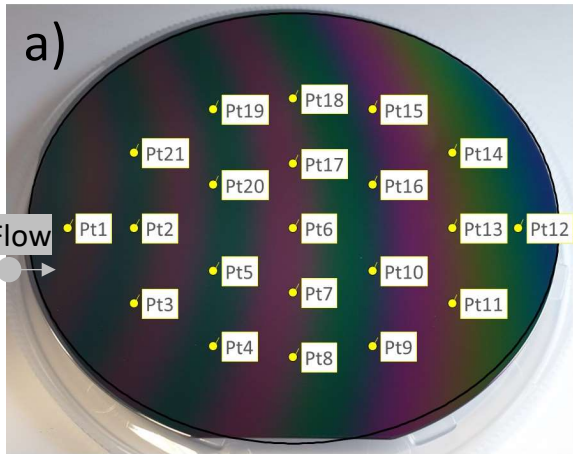
Wagner et al. (2016) ACS Combinatorial Science, 18(3) 154

COMBINATORIAL WITH 3 ELEMENTS



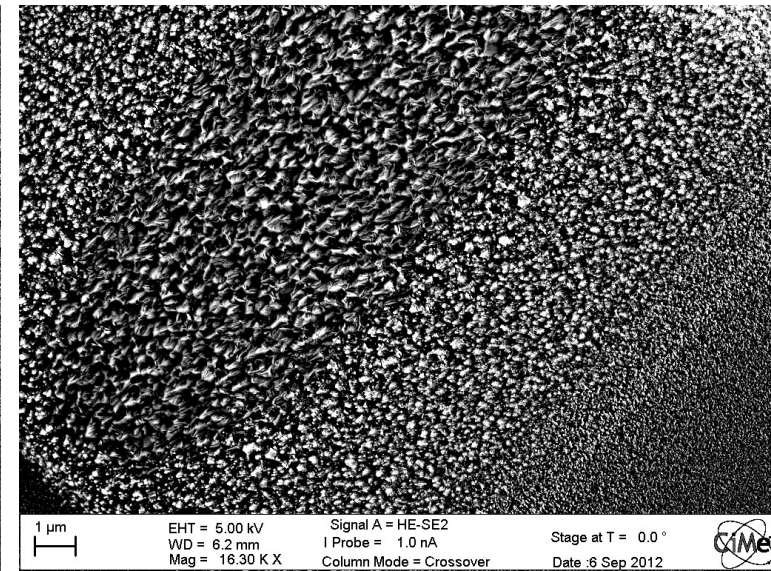
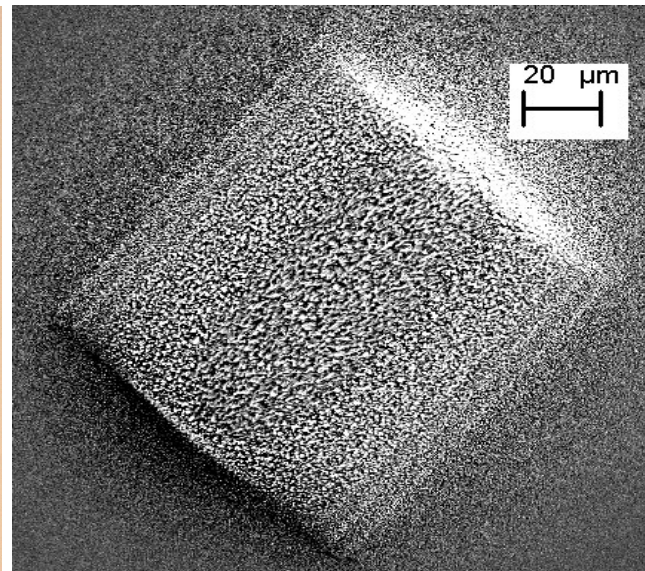
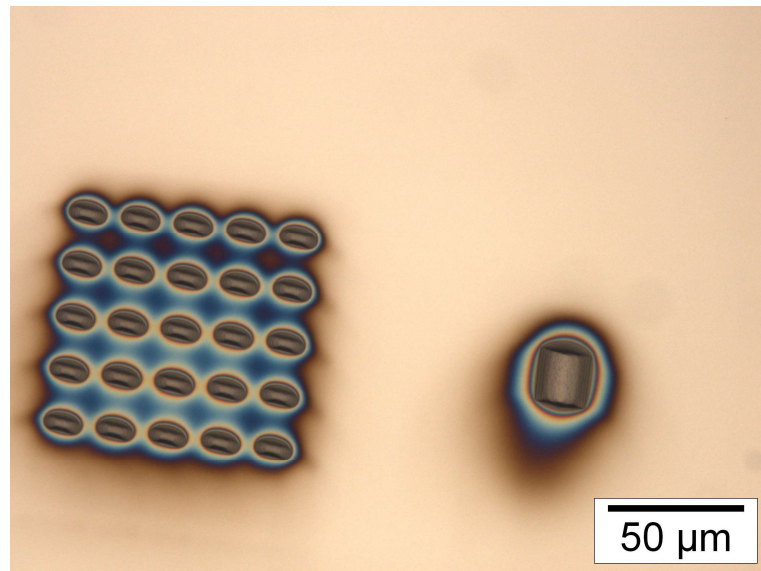
SIMULATION VS EXPERIMENTAL DATA

COMBINATORIAL IN-SITU SPECTRAL REFLECTOMETRY



Mass Transport Limited Regime conditions

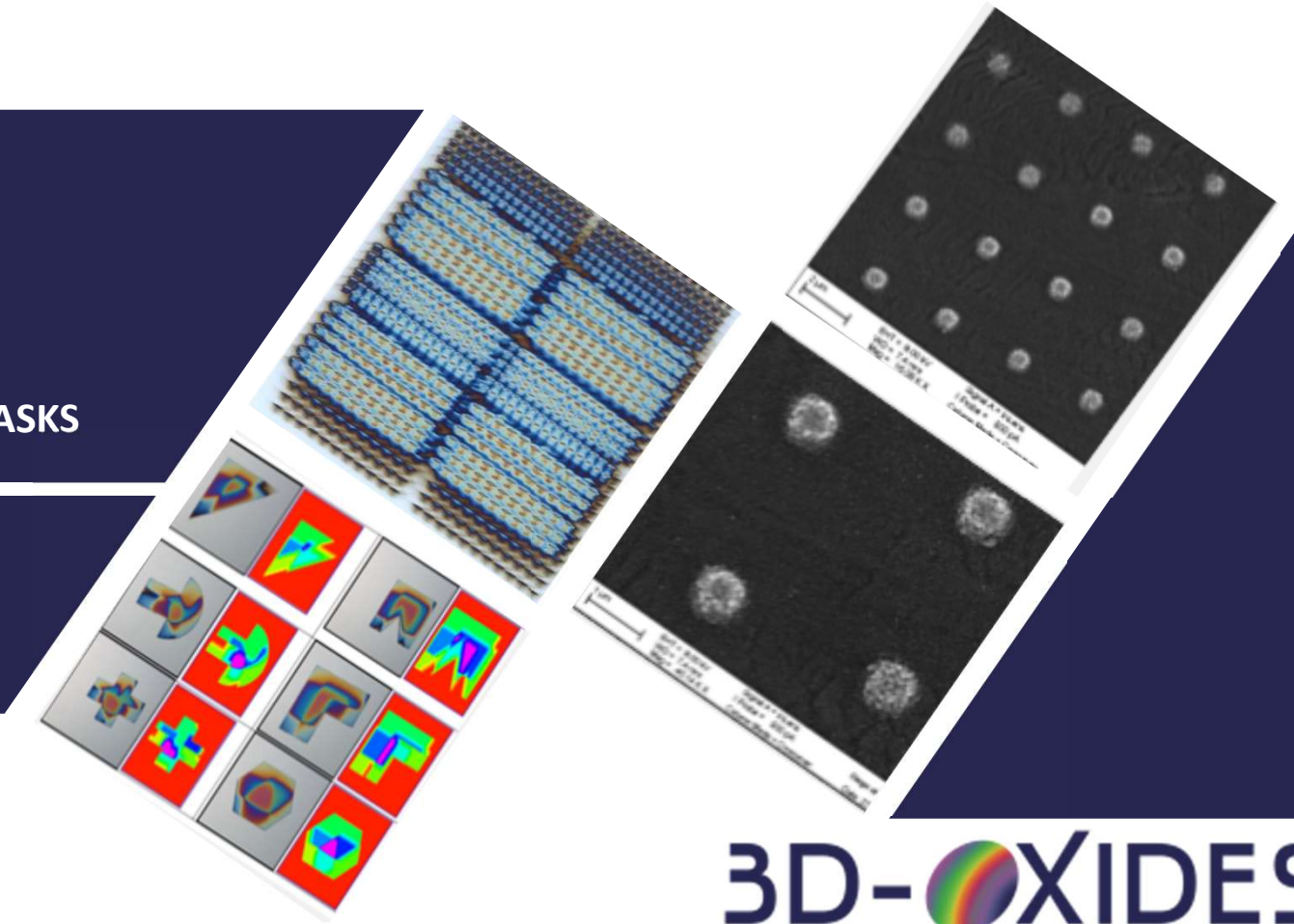
3D-PYRAMID LIKE STRUCTURE



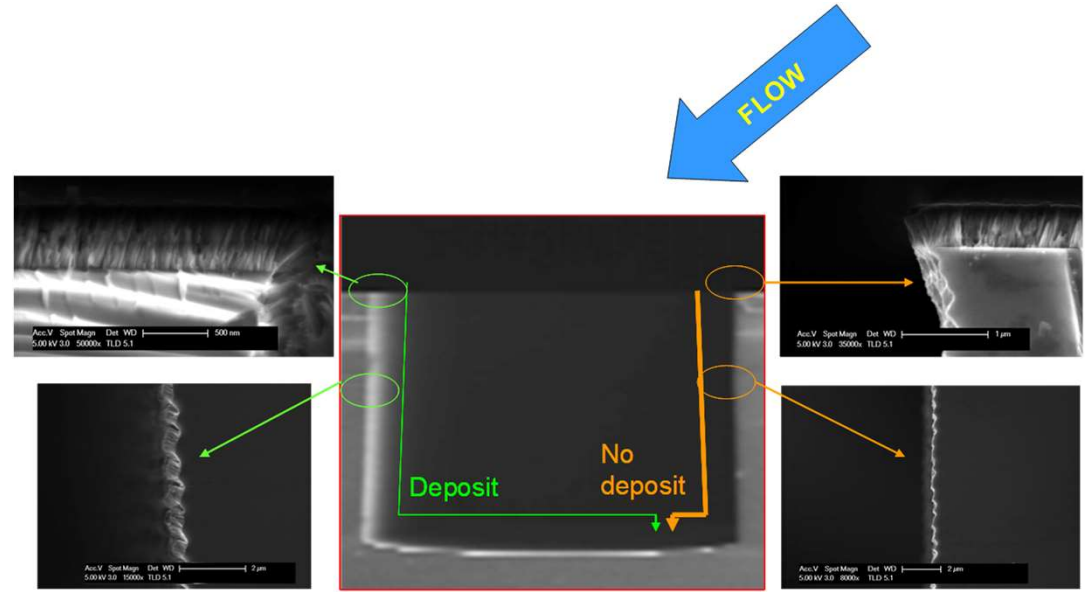
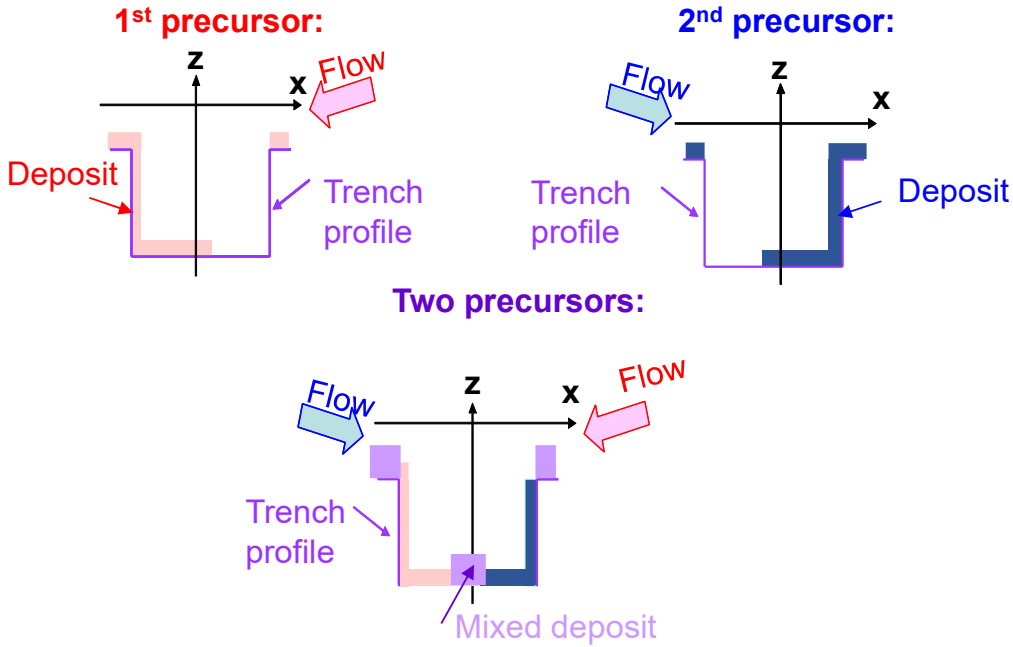
ROUGHNESS INCREASING WITH THICKNESS FOR
COLUMNAR GROWN TiO_2 ANATASE

ADDITIVE GROWTH

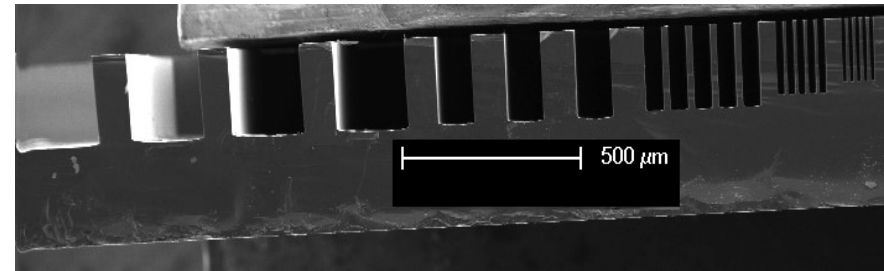
PATTERNED SUBSTRATES / STENCIL MASKS



3D-OXIDES
MULTI-FUNCTIONAL THIN FILMS

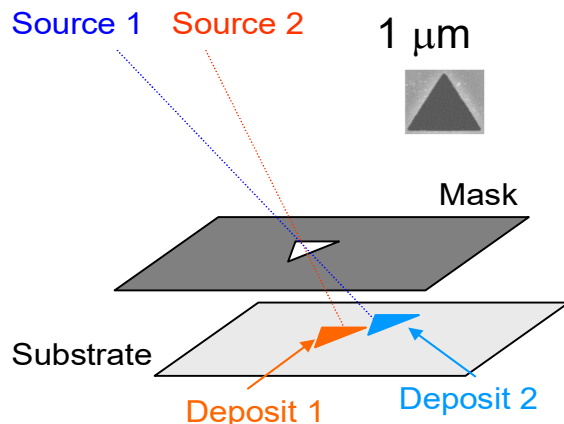


Deposition on patterned substrates

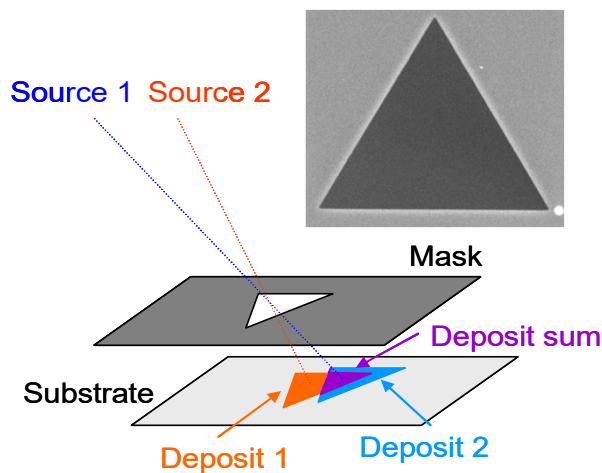
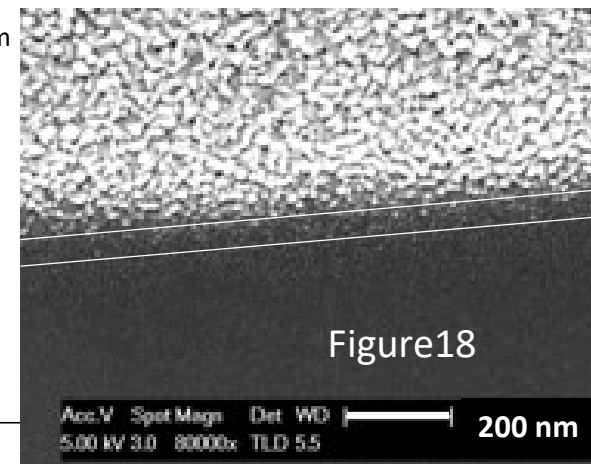
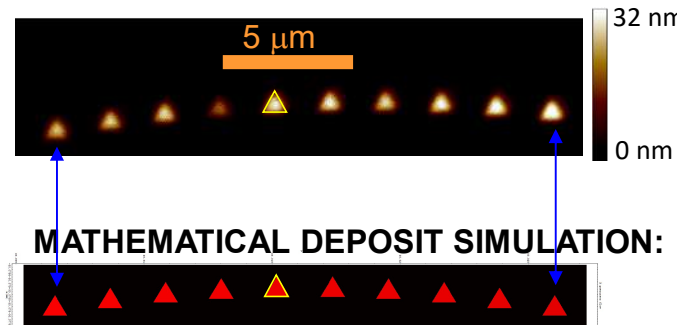


MORPHOLOGICAL PATTERNING

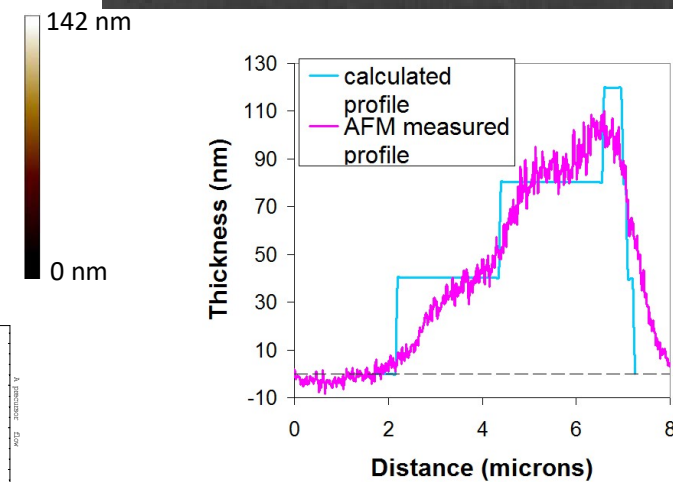
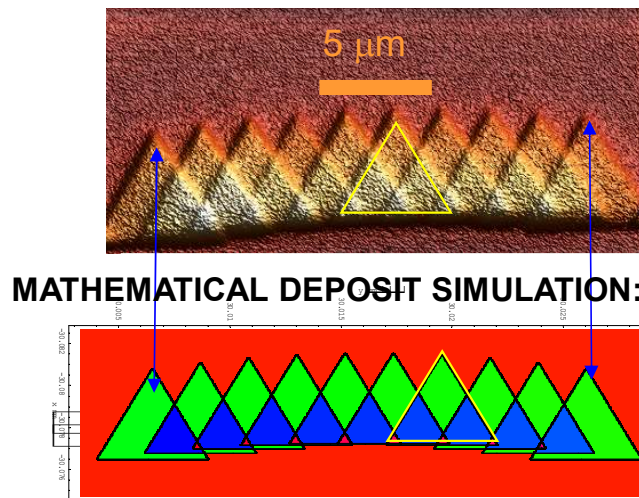
Wagner et al. (2015) *Thin Solid Films* 586 64



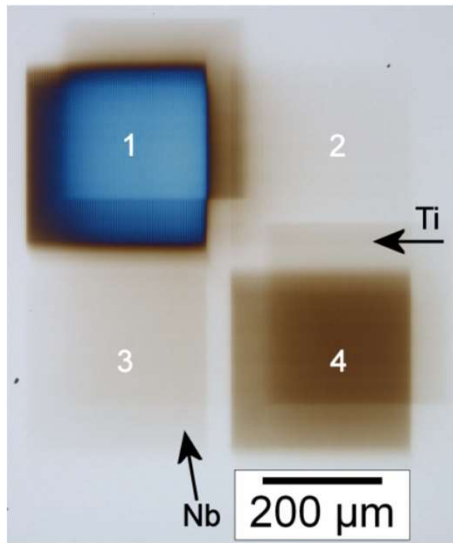
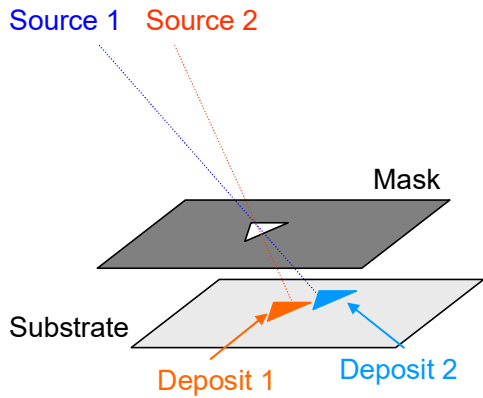
DEPOSIT AFM MEASUREMENT:



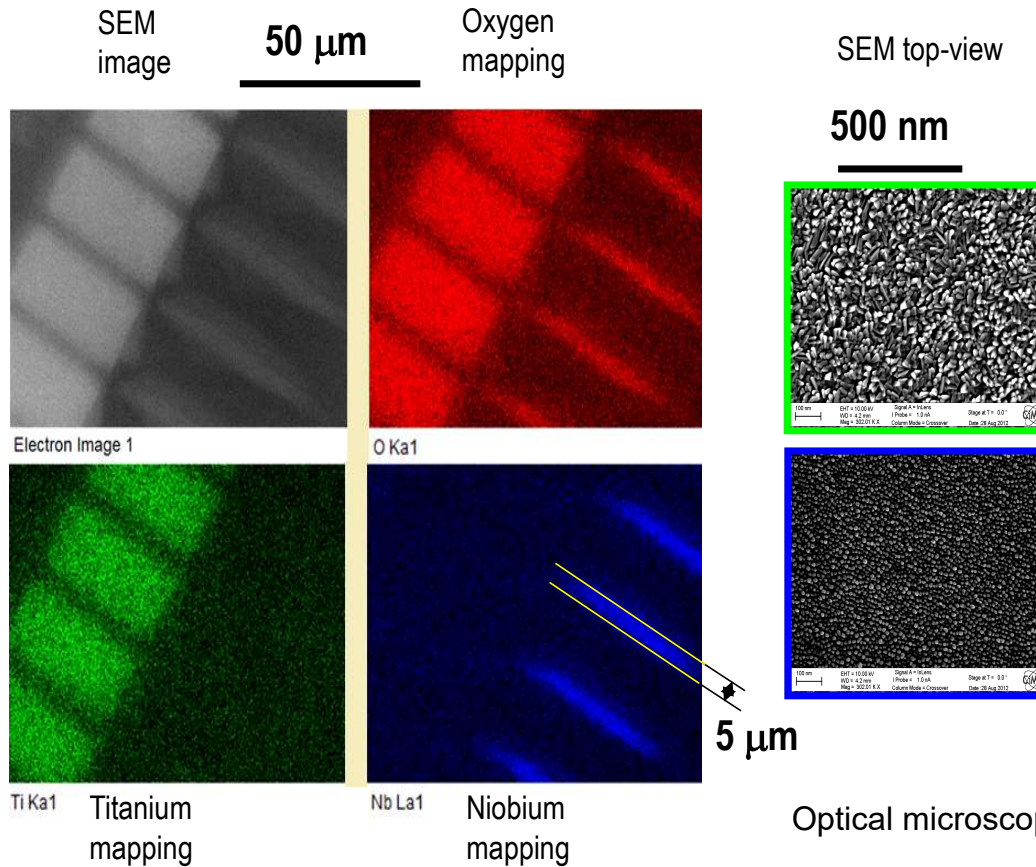
DEPOSIT AFM MEASUREMENT:



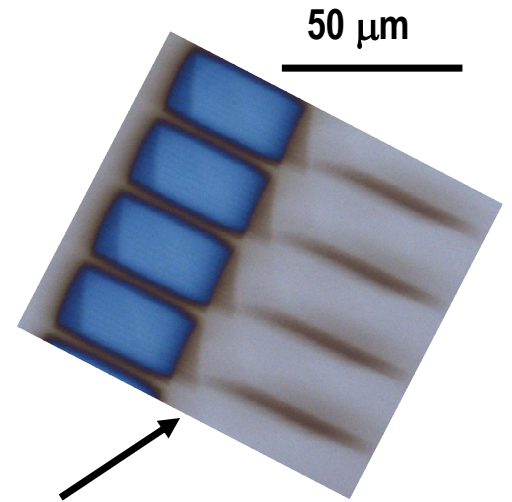
CHEMICAL PATTERNING (SEPARATED ELEMENTS)



EDX mapping



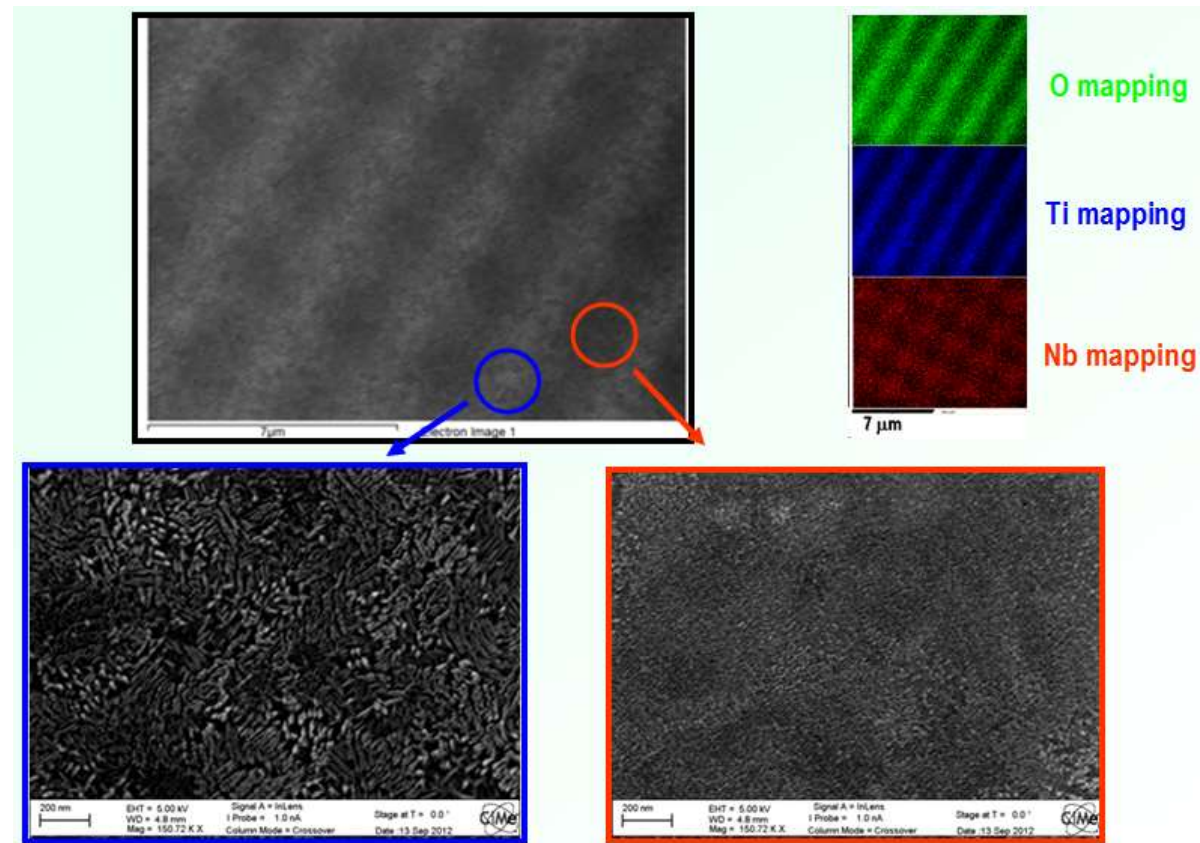
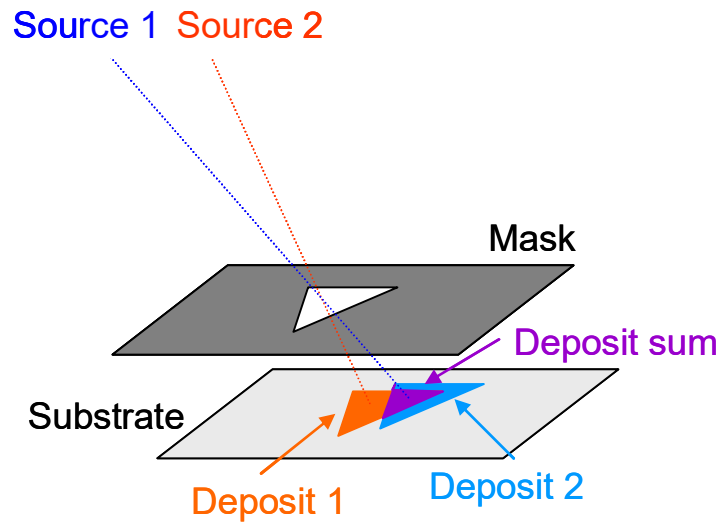
Optical microscopy



Optical microscope picture of the layer 80 nm for TiO₂, 40 nm for Nb₂O₅

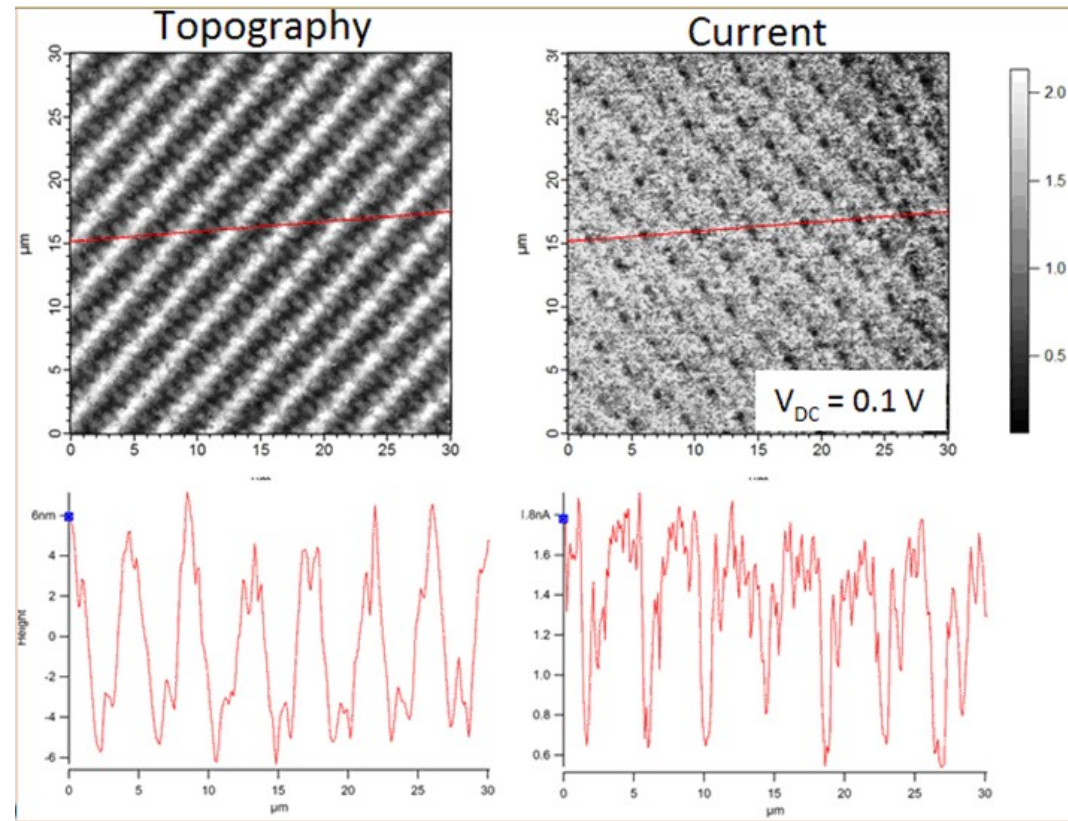
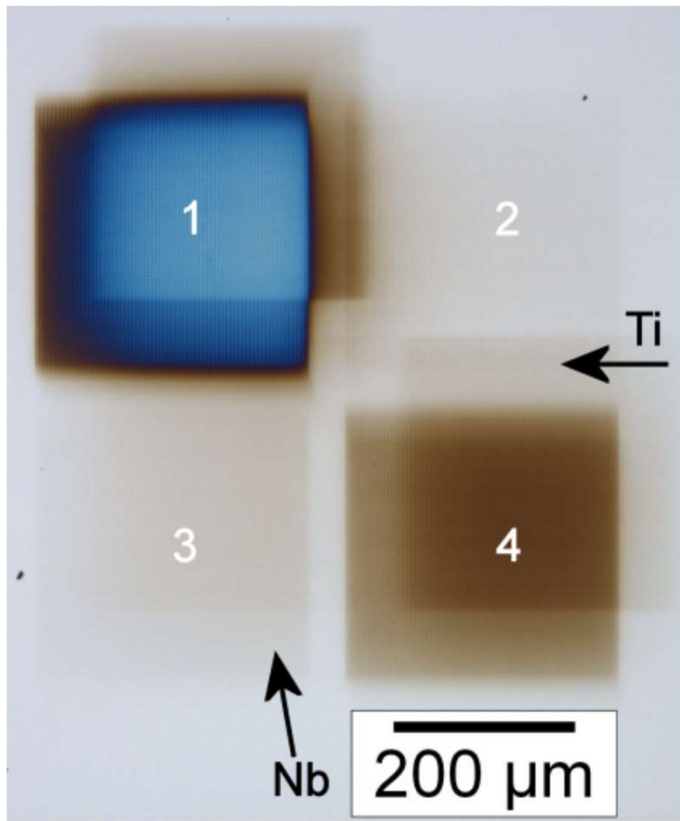


CHEMICAL PATTERNING (SUPERPOSED ELEMENTS)



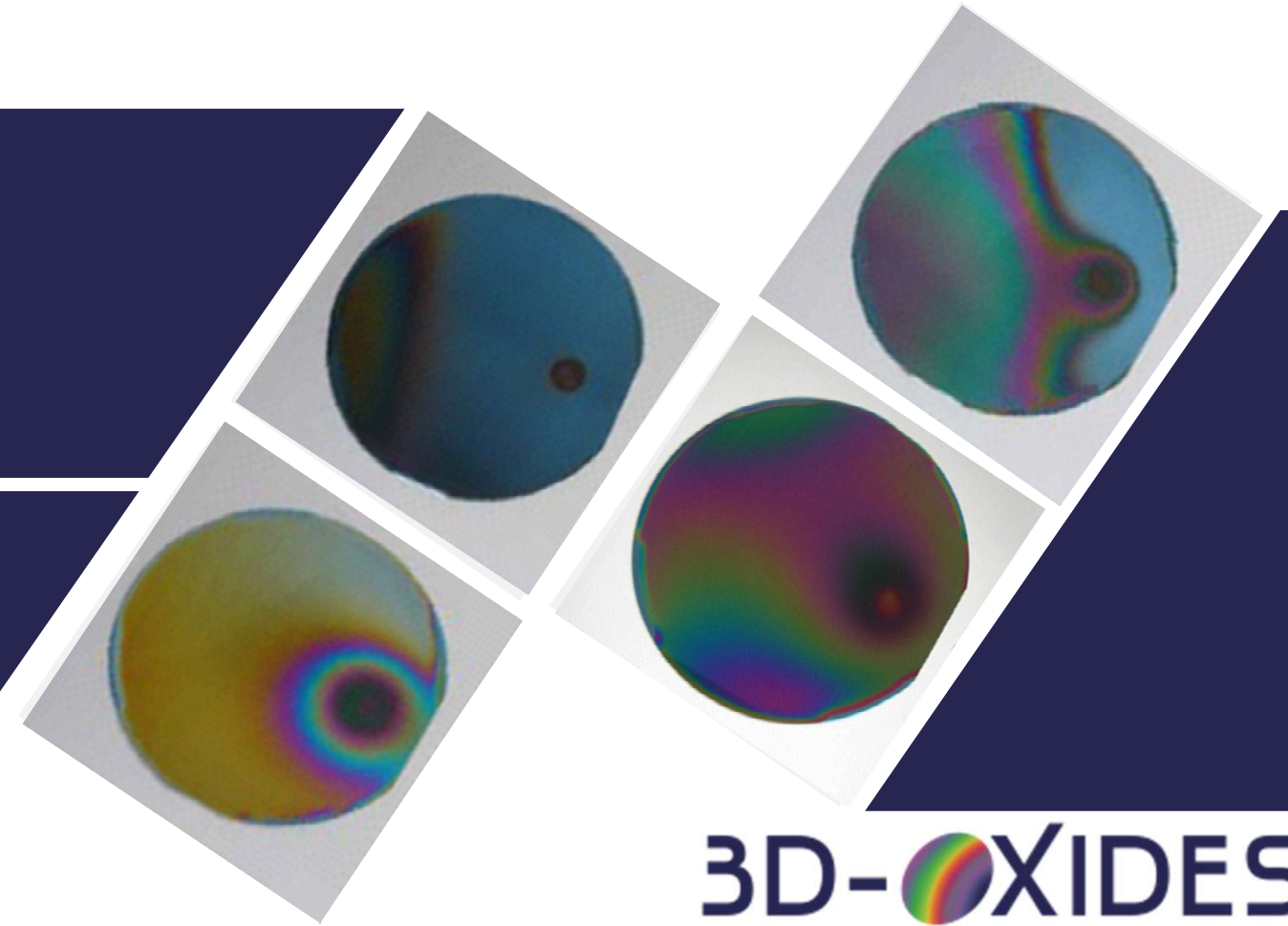
FUNCTIONAL PROPERTIES PATTERNING

Variable electrical conductivity.
Most functional properties can be modulated and patterned.



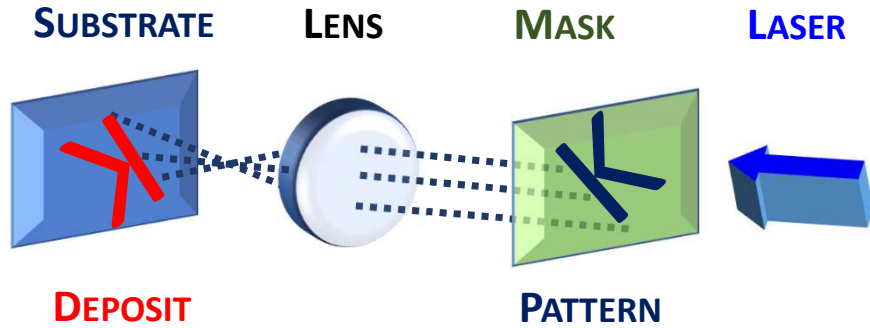
ADDITIVE GROWTH

CBE-LASER-ASSISTED



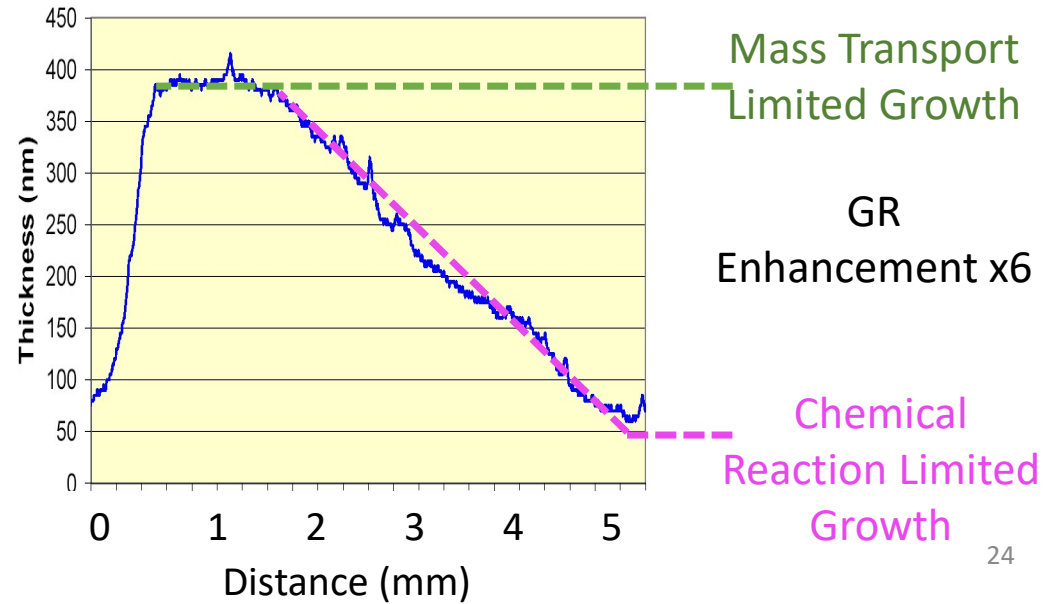
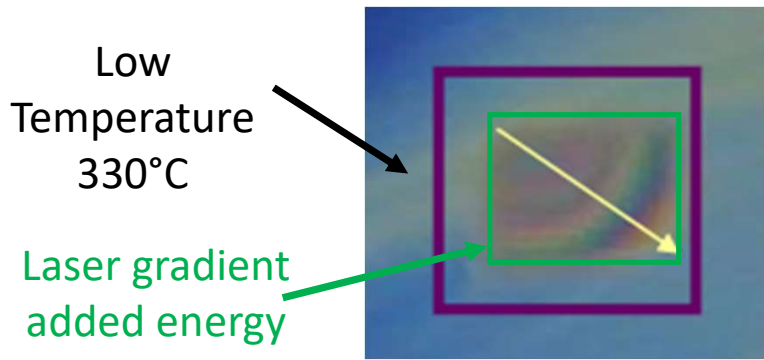
3D-OXIDES
MULTI-FUNCTIONAL THIN FILMS

LASER PATTERNING (GROWTH RATES)



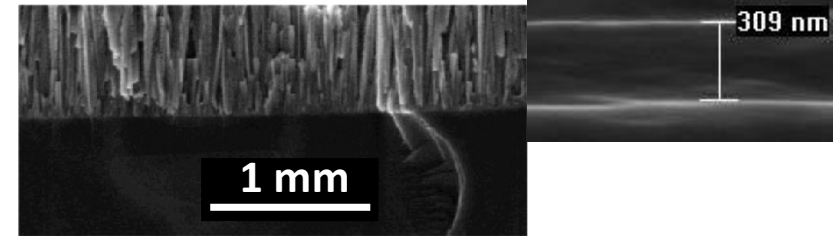
| ENERGY Source | Thin Film Colour | TiO ₂ layer (thickness nm) |
|--------------------|------------------|---------------------------------------|
| Thermal deposition | Blue | 70.0 |
| Fluence 1 | Yellow | 112.7 |
| Fluence 2 | Blue | 190.3 |
| Fluence 3 | Red | 360.6 |
| Fluence 4 | Blue | 402.1 |

DEPOSITION / ABLATION / ETCHING
IS LIMITED TO THE IRRADIATED AREA

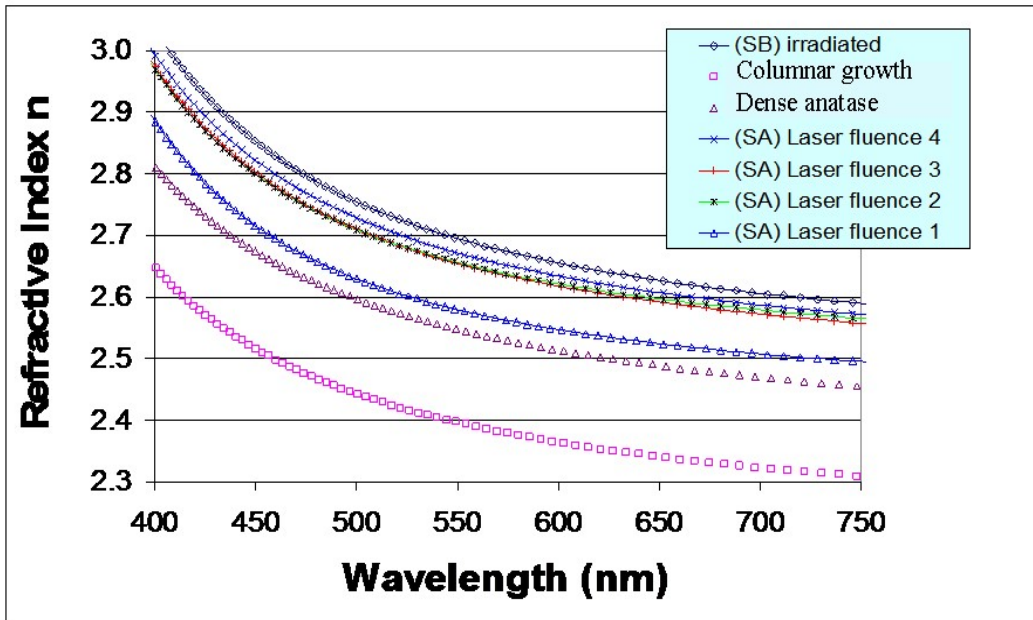


Selective modification of TiO₂ thin films properties

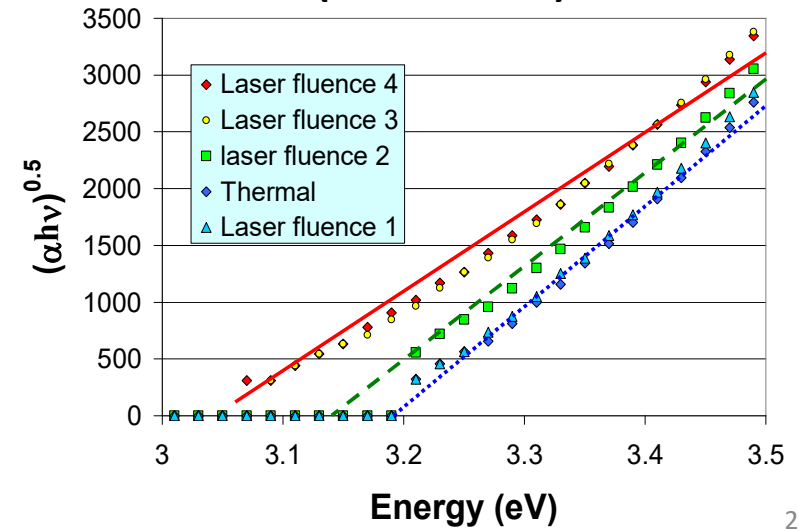
Film densification



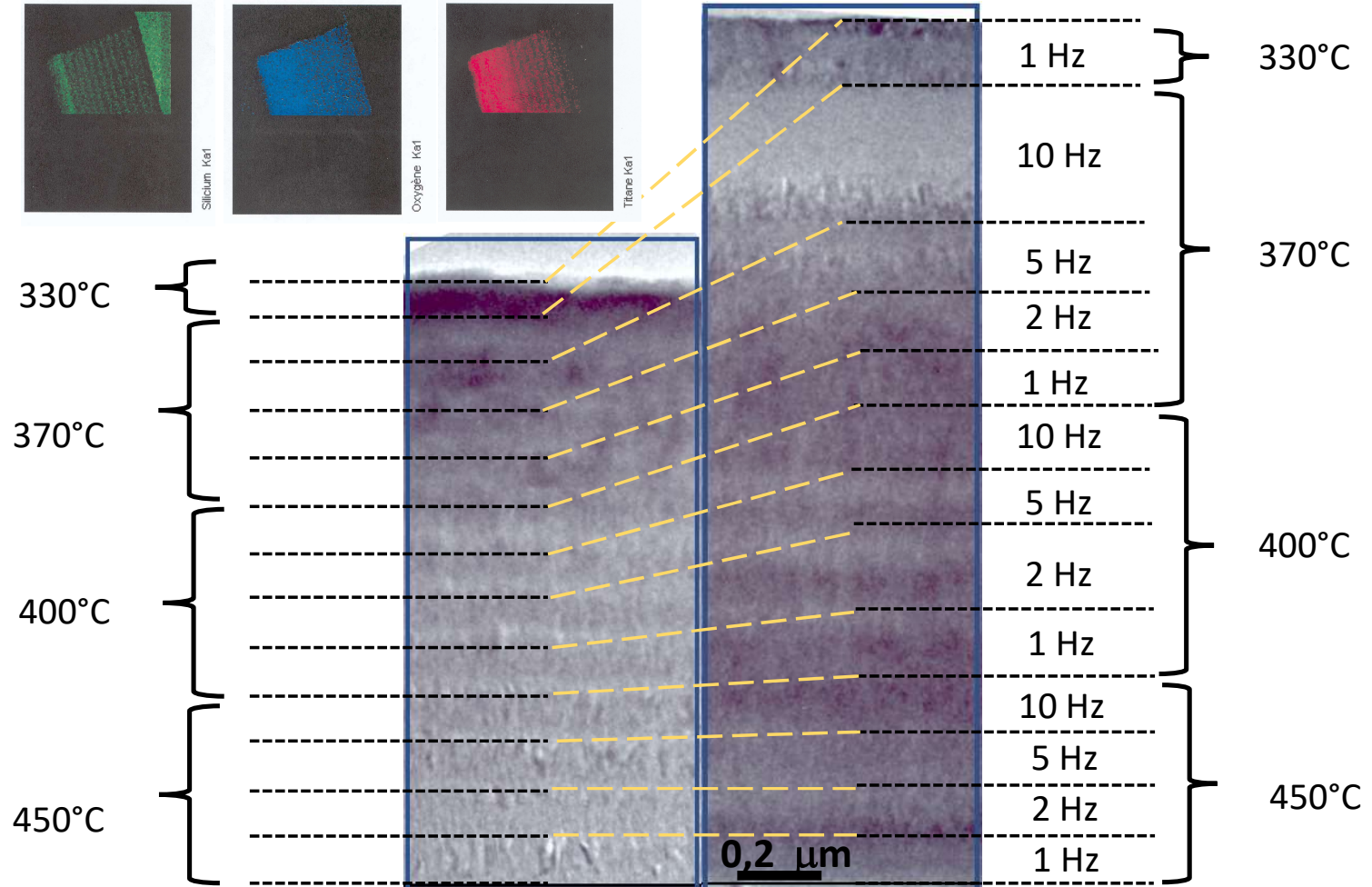
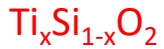
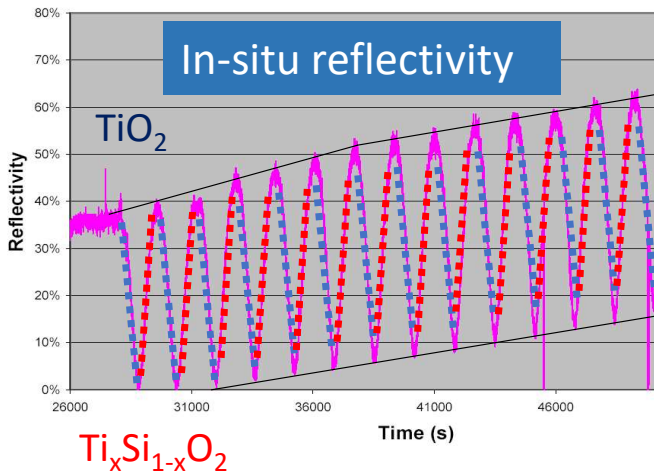
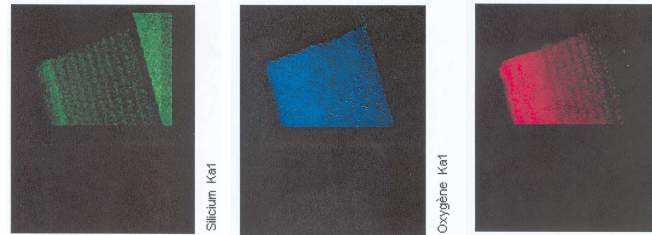
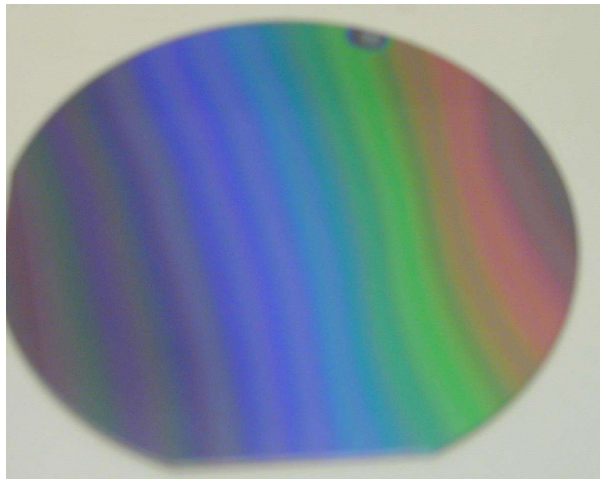
Refractive index fine tuning



BandGap shifting (Tauc Model)



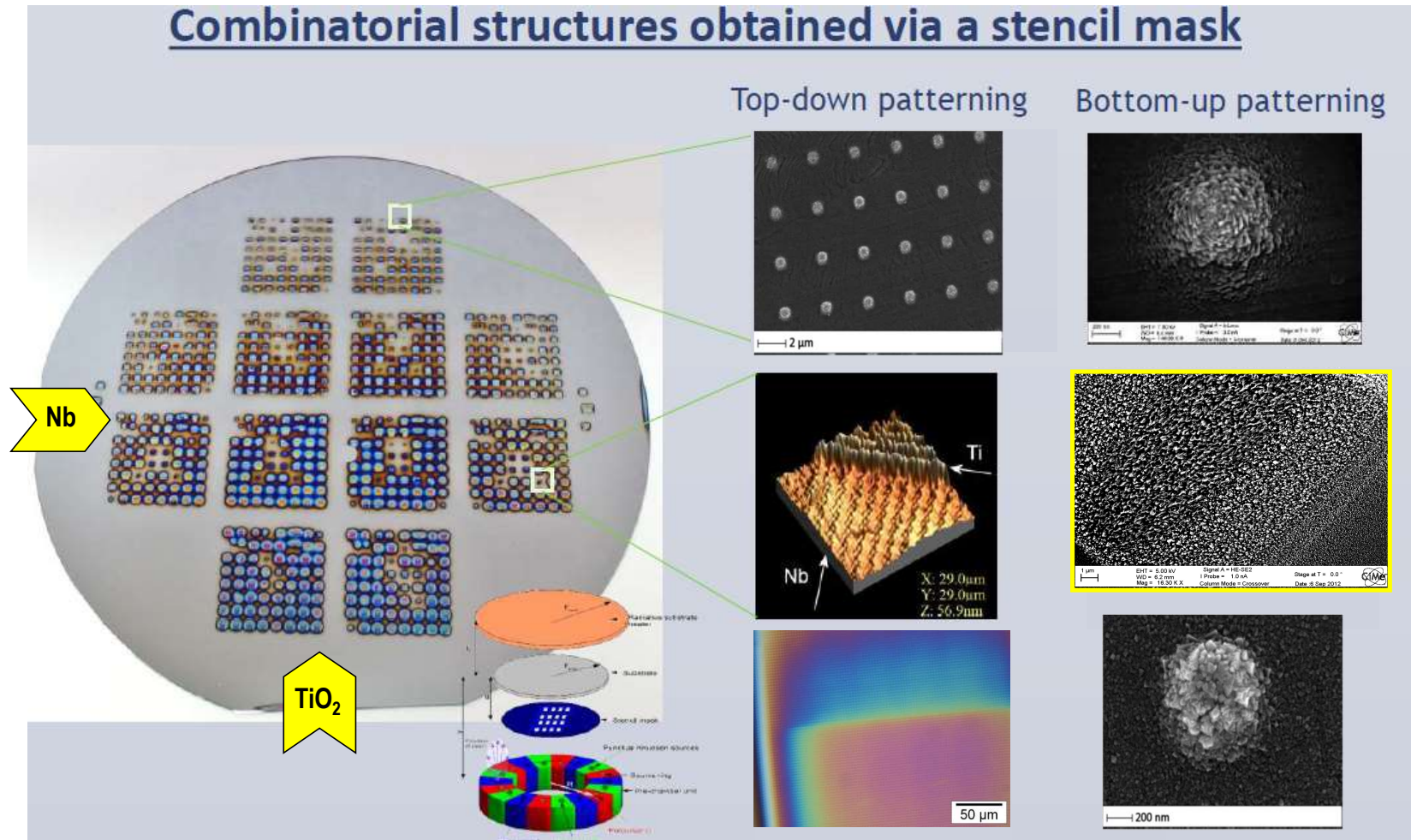
LASER 3D-PATTERNING (CHEMICAL COMPOSITION)



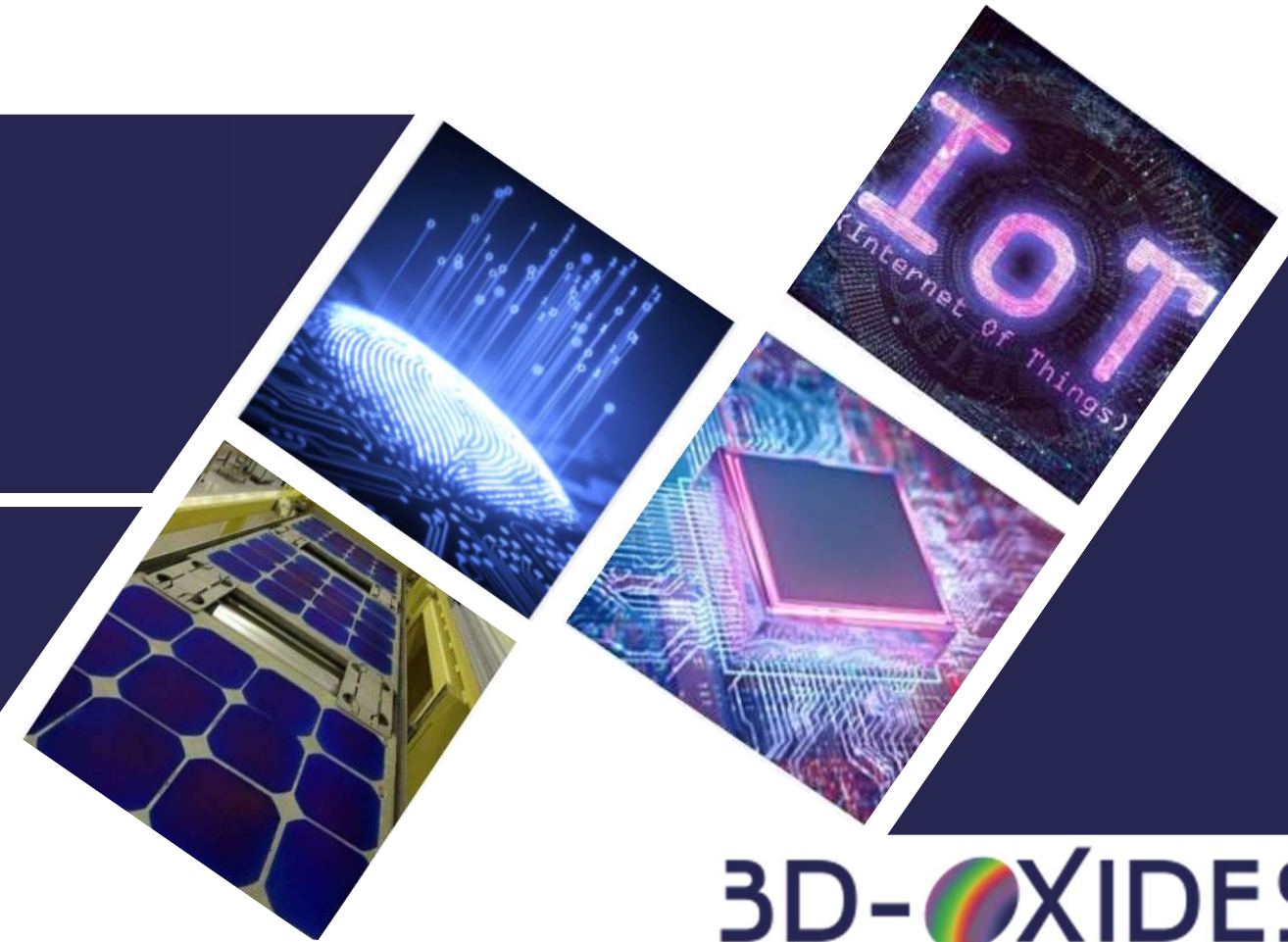
THERMAL GROWTH THERMAL GROWTH + LASER²⁶

Additive growth

Some Applications

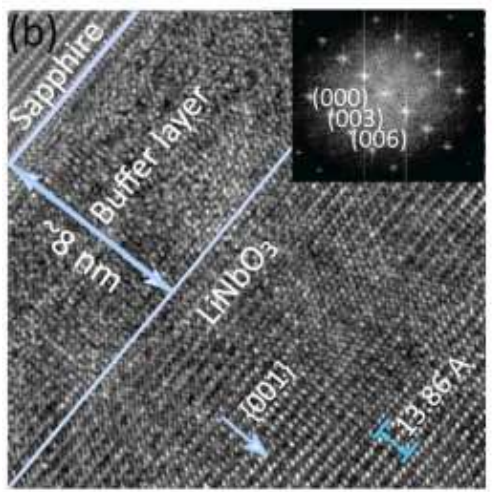


FUNCTIONAL MATERIALS



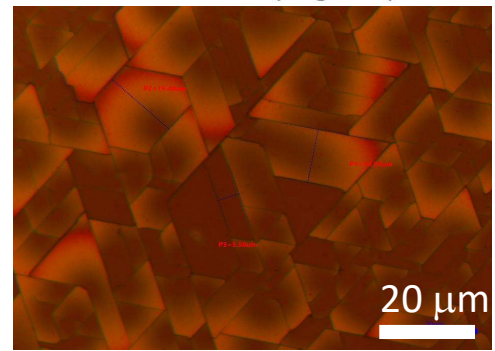
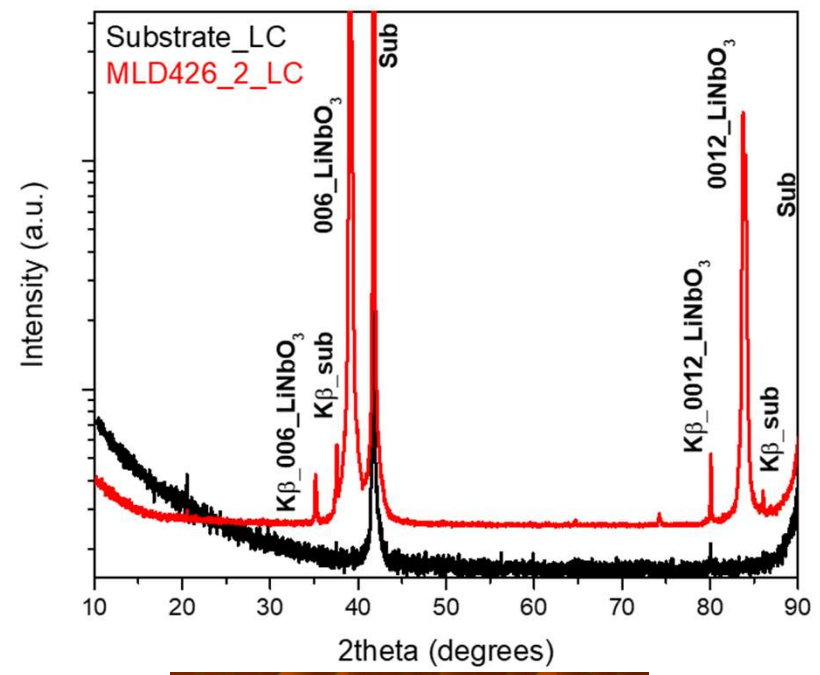
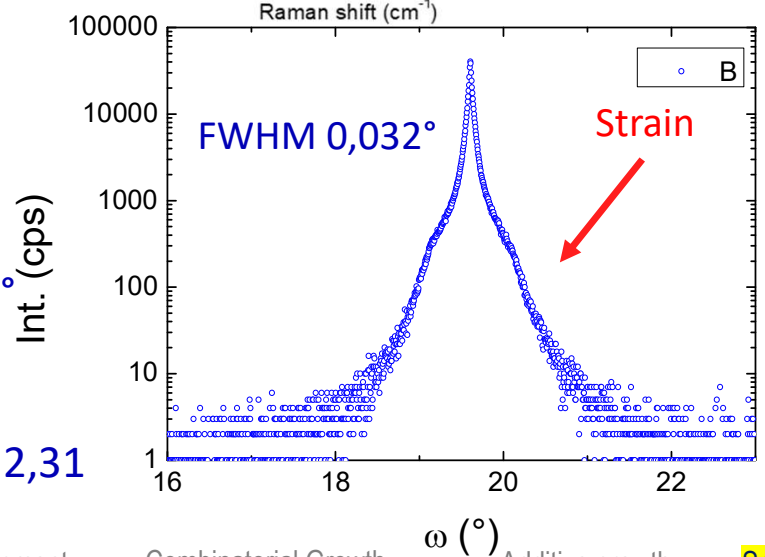
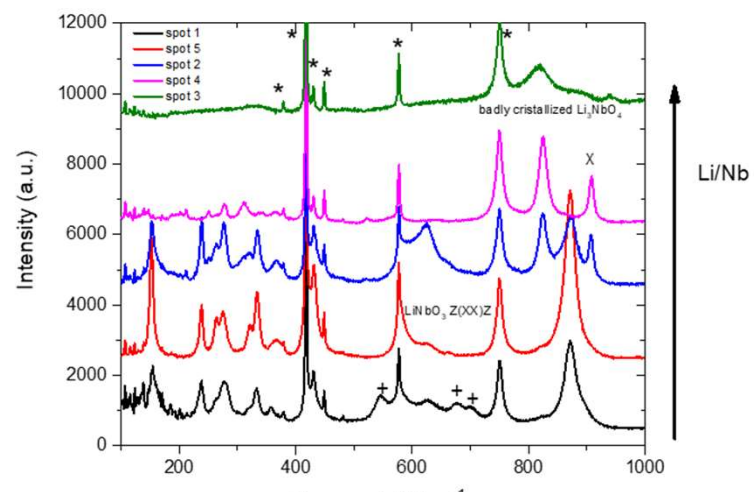
3D-OXIDES
MULTI-FUNCTIONAL THIN FILMS

LiNbO₃

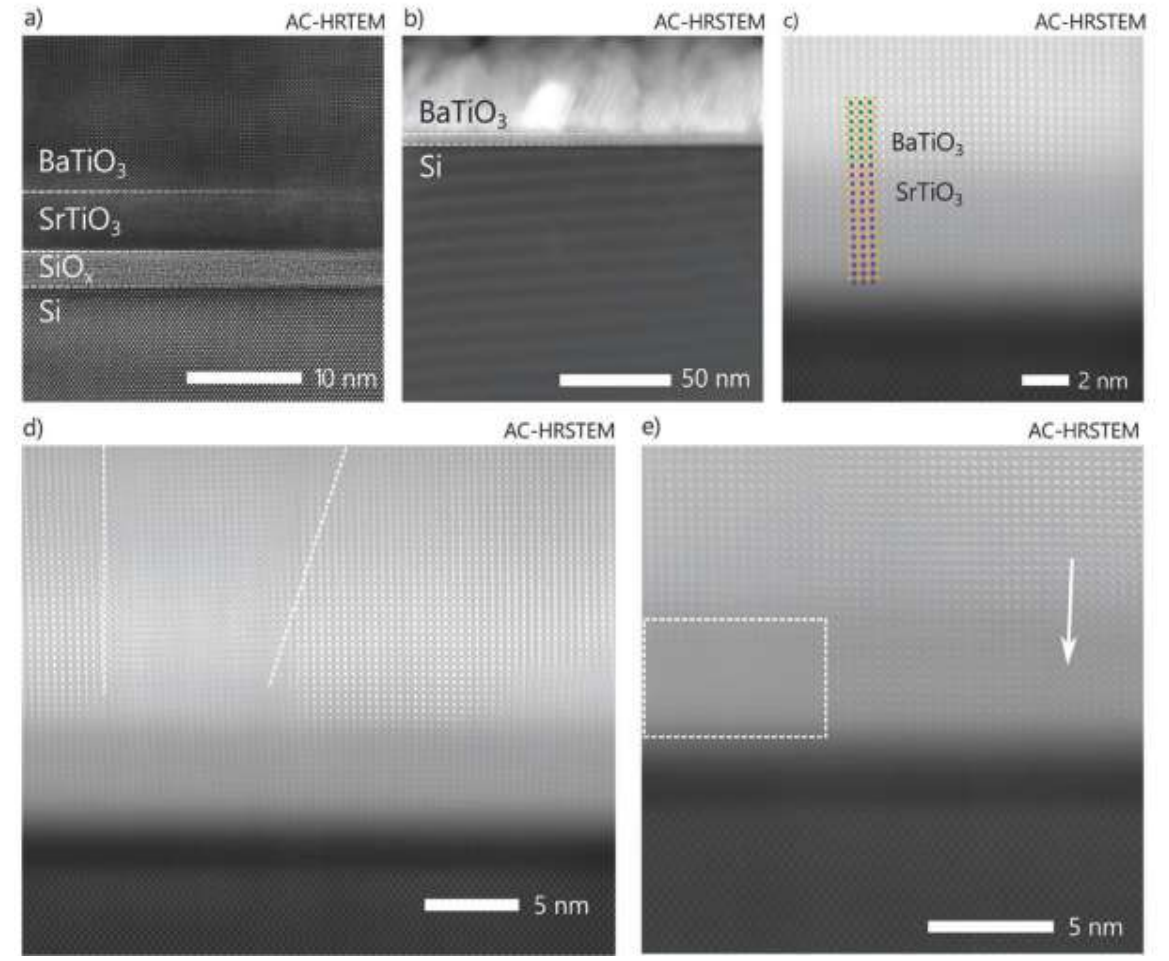
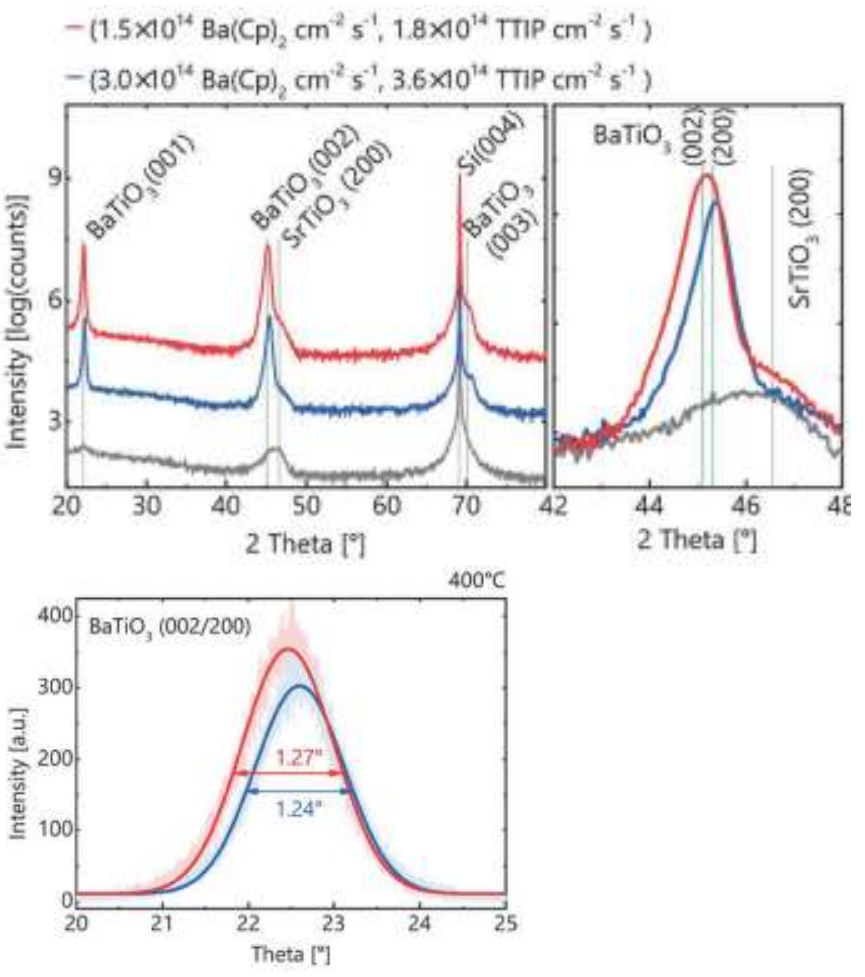


Combinatorial Chemical Beam Epitaxy of Lithium Niobate Thin Films on Sapphire
A. Dabirian, et Al.; Journal of The Electrochemical Society, 158 (2) D72-D76 (2011).
DOI: [10.1149/1.3519843](https://doi.org/10.1149/1.3519843)

- Single orientation 006/0012
- Rocking curves: FWHM 0,03°
- Roughness RMS 1,39 nm
- Raman: ok
- Refractive index: $2,26 < n < 2,31$



EPITAXIAL BaTiO₃ ON SI (EPFL AND IBM)



Reference: Low Temperature Epitaxial Barium Titanate Thin Film Growth in High Vacuum CVD; M. Reinke et Al; Adv. Mater. Interfaces 2017, 1700116 DOI: 10.1002/admi.201700116

CONCLUSION & OUTLOOK



3D-OXIDES
MULTI-FUNCTIONAL THIN FILMS

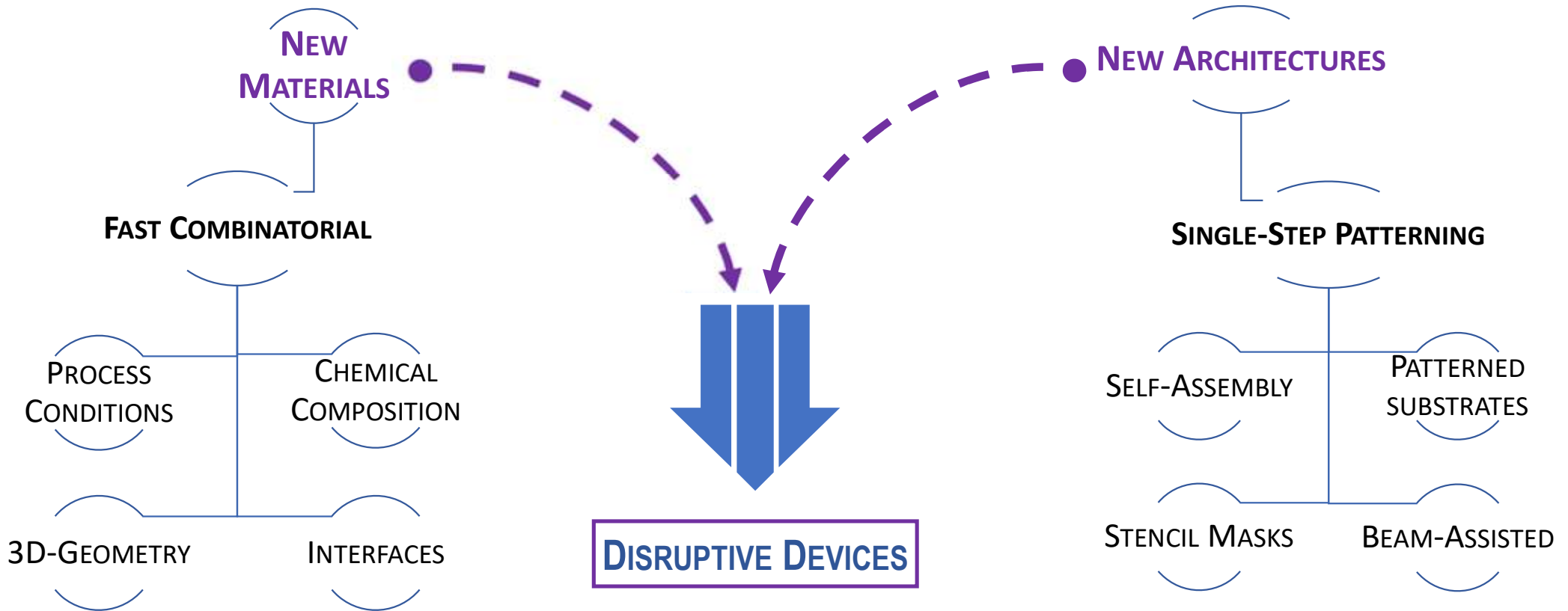
Top level properties on many different materials:

LiNbO_3 , BaTiO_3 , SrTiO_3 , TiO_2 , $\text{Hf}_{(1-x-y)}\text{Ti}_x\text{Zr}_y\text{O}_2$, Nb_2O_5 , Ta_2O_5 , Al_2O_3 , ZnO , Vo_x , etc...

Upscalable to production

1. Very high control accuracy on process
2. Lower thermal budget (CMOS compatible)
3. Large substrates (mass production)
4. More elaborated architectures for better devices

A DISRUPTIVE TOOL FOR NEW OXIDE THIN FILMS DEVICES



FAST TECHNOLOGICAL APPROACH ADDRESSING SIMULTANEOUSLY SEVERAL MARKETS

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THANK YOU FOR YOUR ATTENTION



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